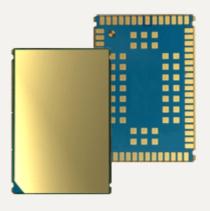


Cinterion® EHS5-E/EHS5-US

Hardware Interface Description

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1 Introduction

This document¹ describes the hardware of the Cinterion[®] EHS5-E/EHS5-US module. It helps you quickly retrieve interface specifications, electrical and mechanical details and information on the requirements to be considered for integrating further components.

1.1 Key Features at a Glance

Feature	Implementation
General	
Frequency bands	EHS5-E: GSM/GPRS/EDGE: Dual band GSM 900/1800MHz UMTS/HSPA+: Dual band UMTS 900/2100MHz EHS5-US: GSM/GPRS/EDGE: Dual band GSM 850/1900MHz UMTS/HSPA+: Dual band UMTS 850/1900MHz
GSM class	Small MS
Output power (according to Release 99, V5)	EHS5-E: Class 4 (+33dBm ±2dB) for EGSM900 Class 1 (+30dBm ±2dB) for GSM1800 Class E2 (+27dBm ± 3dB) for GSM 900 8-PSK Class E2 (+26dBm +3 /-4dB) for GSM 1800 8-PSK Class 3 (+24dBm +1/-3dB) for UMTS 2100, WCDMA FDD Bdl Class 3 (+24dBm +1/-3dB) for UMTS 900, WCDMA FDD BdVIII EHS5-US: Class 4 (+33dBm ±2dB) for EGSM850 Class 1 (+30dBm ±2dB) for GSM1900 Class E2 (+27dBm ± 3dB) for GSM 850 8-PSK Class E2 (+26dBm +3 /-4dB) for GSM 1900 8-PSK Class 3 (+24dBm +1/-3dB) for UMTS 1900, WCDMA FDD BdII Class 3 (+24dBm +1/-3dB) for UMTS 850, WCDMA FDD BdV
Power supply	3.3V to 4.5V
Operating temperature (board temperature)	Normal operation: -30°C to +85°C Extended operation: -40°C to +90°C
Physical	Dimensions: 27.6mm x 18.8mm x 2.2mm Weight: approx. 3g
RoHS	All hardware components fully compliant with EU RoHS Directive

^{1.} The document is effective only if listed in the appropriate Release Notes as part of the technical documentation delivered with your Cinterion product.

Feature	Implementation				
HSPA features					
3GPP Release 6, 7	DL 7.2Mbps, UL 5.7Mbps HSDPA Cat.8 / HSUPA Cat.6 data rates Compressed mode (CM) supported according to 3GPP TS25.212				
UMTS features					
3GPP Release 4	PS data rate – 384 kbps DL / 384 kbps UL CS data rate – 64 kbps DL / 64 kbps UL				
GSM/GPRS/EGPRS feate	ures				
Data transfer	 GPRS: Multislot Class 12 Full PBCCH support Mobile Station Class B Coding Scheme 1 – 4 EGPRS: Multislot Class 12 EDGE E2 power class for 8 PSK Downlink coding schemes – CS 1-4, MCS 1-9 Uplink coding schemes – CS 1-4, MCS 1-9 SRB loopback and test mode B 8-bit, 11-bit RACH PBCCH support 1 phase/2 phase access procedures Link adaptation and IR NACC, extended UL TBF Mobile Station Class B CSD: V.110, RLP, non-transparent 9.6kbps USSD 				
SMS	Point-to-point MT and MO Cell broadcast Text and PDU mode Storage: SIM card plus SMS locations in mobile equipment				
Software					
AT commands	Hayes 3GPP TS 27.007, TS 27.005, Cinterion AT commands for RIL compatibility (available as of Release 2)				
Microsoft [™] compatibility	RIL for Pocket PC and Smartphone (available as of Release 2)				
SIM Application Toolkit	SAT Release 99 (available as of Release 2)				
Firmware update	Generic update from host application over ASC0 or USB modem.				

Feature	Implementation			
Interfaces				
Module interface	Surface mount device with solderable connection pads (SMT application interface). Land grid array (LGA) technology ensures high solder joint reliability and provides the possibility to use an optional module mounting socket. For more information on how to integrate SMT modules see also [4]. This application note comprises chapters on module mounting and application layout issues as well as on SMT application development equipment.			
USB	USB 2.0 High Speed (480Mbit/s) device interface, Full Speed (12Mbit/s) compliant			
2 serial interfaces	 ASC0: 8-wire modem interface with status and control lines, unbalanced, asynchronous Adjustable baud rates: 1,200bps to 921,600bps Autobauding: 1,200bps to 230,400bps Supports RTS0/CTS0 hardware flow control. Multiplex ability according to GSM 07.10 Multiplexer Protocol. ASC1: 4-wire, unbalanced asynchronous interface Autobauding: 1,200bps to 230,400bps Adjustable baud rates: 1,200bps to 921,600bps Supports RTS1/CTS1 hardware flow control 			
Audio	1 digital interface (PCM)			
UICC interface	Supported SIM/USIM cards: 3V, 1.8V			
GPIO interface	GPIO interface with 5 GPIO lines. The GPIO interface is shared with LED signalling, PWM and fast shutdown functionality (available as of Release 2).			
I ² C interface	Supports I ² C serial interface (available as of Release 2)			
Antenna interface pads	50Ω			
Power on/off, Reset				
Power on/off	Switch-on by hardware signal ON and AUTO_ON Switch-off by AT command Switch off by hardware signal GPIO4/FST_SHDN instead of AT command (available as of Release 2) Automatic switch-off in case of critical temperature and voltage conditions.			
Reset	Orderly shutdown and reset by AT command Emergency reset by hardware signal EMERG_RST			
Special features				
Real time clock	Timer functions via AT commands			
Phonebook	SIM and phone			
TTY/CTM support	Integrated CTM modem			
Evaluation kit				
Evaluation module EHS5-E/EHS5-US module soldered onto a dedicated PCB that of nected to an adapter in order to be mounted onto the DSB75.				
DSB75 DS				

1.2 EHS5-E/EHS5-US System Overview

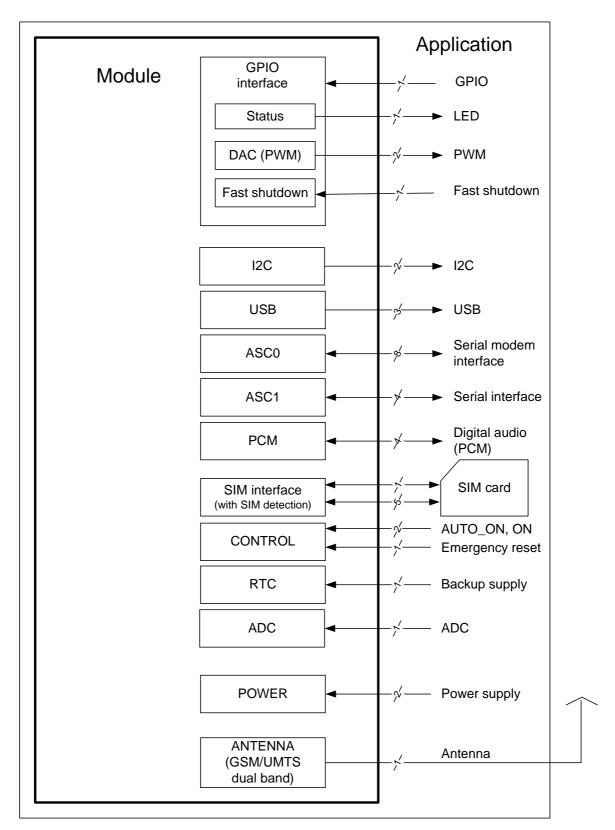


Figure 1: EHS5-E/EHS5-US system overview

1.3 Circuit Concept

The following figures show block diagrams of the EHS5-E/EHS5-US module and illustrate the major functional components:

Baseband block (see Figure 2):

- GSM baseband processor and power management
- Stacked flash/PSRAM memory
- Application interface (SMT with connecting pads)

GSM/UMTS RF section (see Figure 3):

- RF transceiver (part of baseband processor IC)
- RF power amplifier/front-end module inc. harmonics filtering
- Receive SAW filters

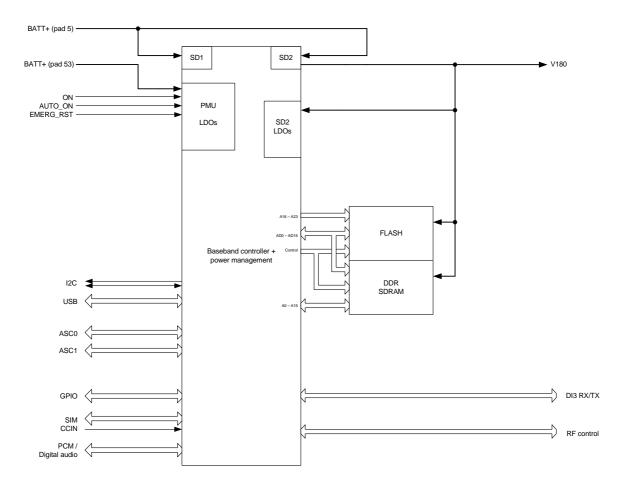


Figure 2: EHS5-E/EHS5-US baseband block diagram

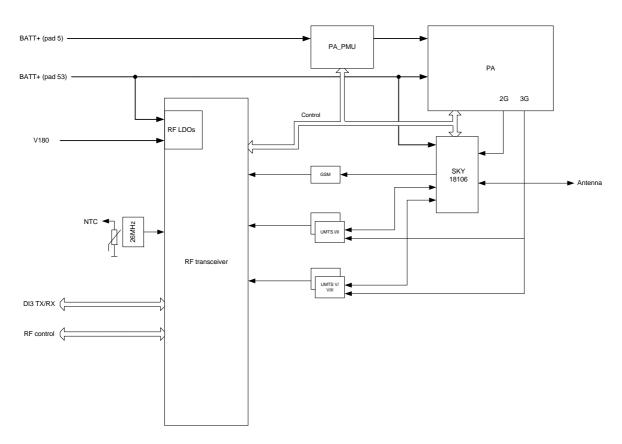


Figure 3: EHS5-E/EHS5-US GSM/UMTS RF section block diagram

2 Interface Characteristics

EHS5-E/EHS5-US is equipped with an SMT application interface that connects to the external application. The SMT application interface incorporates the various application interfaces as well as the RF antenna interface.

2.1 Application Interface

2.1.1 Pad Assignment

The SMT application interface on the EHS5-E/EHS5-US provides connecting pads to integrate the module into external applications. Figure 4 shows the connecting pads' numbering plan, the following Table 1 lists the pads' assignments.

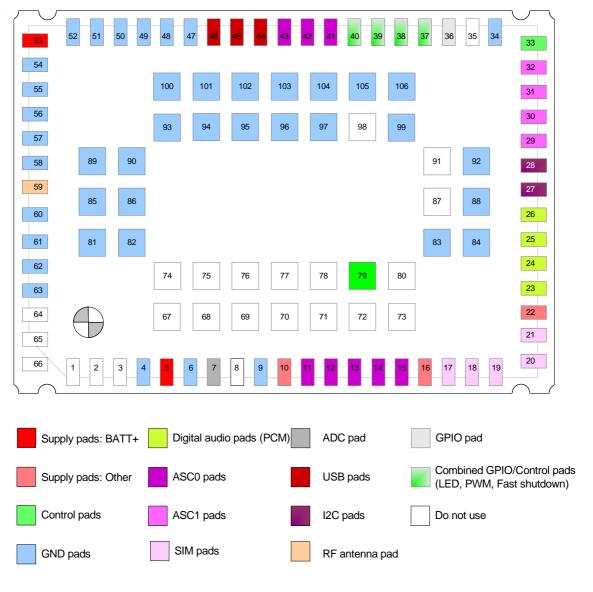


Figure 4: Numbering plan for connecting pads (bottom view)

Table 1: Pad assignments

Pad no.	Signal name	Pad no.	Signal name	Pad no.	Signal name
1	Do not use	23	TXDDAI	45	USB_DP
2	Do not use	24	TFSDAI	46	USB_DN
3	Do not use	25	RXDDAI	47	GND
4	GND	26	SCLK	48	GND
5	BATT+	27	I2CDAT	49	GND
6	GND	28	I2CCLK	50	GND
7	ADC1	29	TXD1	51	GND
8	ON	30	RXD1	52	GND
9	GND	31	RTS1	53	BATT+
10	V180	32	CTS1	54	GND
11	RXD0	33	EMERG_RST	55	GND
12	CTS0	34	GND	56	GND
13	TXD0	35	Do not use	57	GND
14	RING0	36	GPIO8	58	GND
15	RTS0	37	GPIO7/PWM1	59	RF_OUT
16	VDDLP	38	GPIO6/PWM2	60	GND
17	CCRST	39	GPIO5/LED	61	GND
18	CCIN	40	GPIO4/FST_SHDN	62	GND
19	CCIO	41	DSR0	63	GND
20	CCVCC	42	DCD0	64	Do not use
21	CCCLK	43	DTR0	65	Do not use
22	VCORE	44	VUSB	66	Do not use
Centrally lo	ocated pads				
67	Do not use	81	GND	95	GND
68	Do not use	82	GND	96	GND
69	Do not use	83	GND	97	GND
70	Do not use	84	GND	98	Do not use
71	Do not use	85	GND	99	GND
72	Do not use	86	GND	100	GND
73	Do not use	87	Do not use	101	GND
74	Do not use	88	GND	102	GND
75	Do not use	89	GND	103	GND
76	Do not use	90	GND	104	GND
77	Do not use	91	Do not use	105	GND
78	Do not use	92	GND	106	GND
79	AUTO_ON	93	GND		
80	Do not use	94	GND		

Signal pads that are not used should not be connected to an external application.

Please note that the reference voltages listed in Table 2 are the values measured directly on the EHS5-E/EHS5-US module. They do not apply to the accessories connected.

2.1.2 Signal Properties

Table 2: Signal properties

Function	Signal name	Ю	Signal form and level	Comment
Power supply	BATT+ GSM activated	I	V_I max = 4.5V V_I norm = 3.8V V_I min = 3.3V during Tx burst on board $I \approx 2.3$ A, during Tx burst (GSM)	Lines of BATT+ and GND must be connected in parallel for supply purposes because higher peak currents may occur. Minimum voltage must
			n Tx = n x 577µs peak current every 4.616ms	not fall below 3.3V including drop, ripple, spikes.
	BATT+ WCDMA activated	I	V _I max = 4.5V V _I norm = 3.8V V _I min = 3.3V during Transmit active. Imax=700mA during Tx	BATT+ assigned to pad 5 requires an additional ESR 150µF capacitor.
Power supply	GND		Ground	Application Ground
External supply voltage	V180	0	Normal operation: V_O norm = 1.80V ±3% I_O max = -10mA SLEEP mode Operation: V_O Sleep = 1.80V ±5% I_O max = -10mA	V180 may be used to supply level shifters at the interfaces or to supply external application cir- cuits. VCORE and V180 should
			CLmax = 100nF	be used for the power indication circuit.
	VCORE	0	Normal operation: V_O norm = 1.2V ±2.5% I_O max = -10mA SLEEP mode Operation: V_O Sleep = 0.9V1.2V ±4% I_O max = -10mA CLmax = 100nF	If unused keep line open.
Ignition	ON	I	V_{IH} max = VDDLP + 0.3V V_{IH} min = 1.2V V_{IL} max = 0.5V	This signal switches the module ON.
			Min low time before rising edge <=100µs	Set this signal low before and after the startup impulse.
			ON high pulse 50μs80μs	
	AUTO_ON	I	V_{OH} max = VDDLP max V_{IH} min = 1.2V V_{IL} max = 0.5V Low level time >= 50 μ s AUTO_ON low level signal	This signal switches the module on. For more information and requirements see also Section 3.2.1
				This line is low level sensitive triggered.
				If unused keep line open.

Table 2: Signal properties

Function	Signal name	Ю	Signal form and level	Comment
Emergency restart	EMERG_RST		$R_{I} \approx 1 k \Omega$, $C_{I} \approx 1 n F$ $V_{OH} max = VDDLP max$ $V_{IH} min = 1.35 V$ $V_{IL} max = 0.3 V at ~200 \mu A$	This line must be driven low by an open drain or open collector driver connected to GND.
			~~ ~~ low impulse width > 10ms	If unused keep line open.
Fast shutdown	FST_SHDN	V_{IH}^{L} min = 1.30V V_{IH} max = 1.85V		This line must be driven low. If unused keep line open. Line shared with GPIO4
RTC backup	VDDLP	I/O	$V_{O} norm = 1.8V$ $I_{O} max = -25 mA$ $V_{I} max = 1.9V$ $V_{I} min = 1.0V$ $I_{I} typ < 1 \mu A$	It is recommended to use a serial resistor between VDDLP and a possible capacitor. If unused keep line open.
USB	VUSB_IN	I	$V_l min = 3V$ $V_l max = 5.25V$ Active ans suspend current: $I_{max} < 100 \mu A$	All electrical characteristics according to USB Implementers' Forum, USB 2.0 Specification. If unused keep line open.
	USB_DN	I/O	Full and high speed signal characteris-	
	USB_DP		tics according USB 2.0 Specification.	
Serial	RXD0	0	V _{OL} max = 0.25V at I = 1mA	If unused keep line open.
Interface ASC0	CTS0	0	V _{OH} min = 1.55V at I = -1mA V _{OH} max = 1.85V	The DSR0 line is driven
	DCD0	0	G	only by an internal pull up or pull down resistor.
	RING0	0		or pair down resistor.
	DSR0	0	Pull down resistor active V_{OL} max = 0.5V at I > 50 μ A Pull up resistor active V_{OH} min = 1.3V at I > -50 μ A	
	TXD0	I	V _{IL} max = 0.35V V _{IH} min = 1.30V V _{IH} max = 1.85V	
	RTS0	I	Pull down resistor active V_{IL} max = 0.35V at > 50 μ A V_{IH} min = 1.30V at < 240 μ A V_{IH} max = 1.85V at < 240 μ A	
	DTR0	I	Pull up resistor active $V_{IL}max = 0.35V$ at $< -200\mu A$ $V_{IH}min = 1.30V$ at $> -50\mu A$ $V_{IH}max = 1.85V$	

Table 2: Signal properties

Function	Signal name	Ю	Signal form and level	Comment
Serial Interface ASC1	RXD1	0	V_{OL} max = 0.25V at I = 1mA V_{OH} min = 1.55V at I = -1mA V_{OH} max = 1.85V V_{IL} max = 0.35V V_{IH} min = 1.30V V_{IH} max = 1.85V	If unused keep line open.
	TXD1	I		
	RTS1	I		
	CTS1	0		
I ² C	I2CCLK	Ю	Open drain IO	According to the I ² C Bus
	I2CDAT	Ю	V_{OL} min = 0.35V at I = -3mA V_{OH} max = 1.85V R external pull up min = 560Ohm V_{IL} max = 0.35V V_{IH} min = 1.3V V_{IH} max = 1.85V	Specification Version 2.1 for the fast mode a rise time of max. 300ns is permitted. There is also a maximum V _{OL} =0.4V at 3mA specified. The value of the pull-up depends on the capacitive load of the whole system (I ² C Slave + lines). The maximum sink current of I2CDAT and I2CCLK is 4mA.
				If lines are unused keep lines open.
GPIO interface	GPIO4	Ю	V _{OL} max = 0.25V at I = 1mA V _{OH} min = 1.55V at I = -1mA V _{OH} max = 1.85V V _{IL} max = 0.335V V _{IH} min = 1.30V V _{IH} max = 1.85V	If unused keep line open. Please note that GPIO lines can be used for functions other than GPIO:
	GPIO5	Ю		
	GPIO6	Ю		
	GPIO7	Ю		
	GPIO8	Ю		Fast shutdown: GPIO4 Status LED line: GPIO5 PWM: GPIO6/GPIO7
Digital audio inter- face (PCM)	TFSDAI	0	V_{OL} max = 0.25V at I = 1mA V_{OH} min = 1.55V at I = -1mA V_{OH} max = 1.85V V_{IL} max = 0.35V V_{IH} min = 1.30V V_{IH} max = 1.85V	If unused keep line open.
	SCLK	0		
	TXDDAI	0		
	RXDDAI	I		
ADC	ADC1	I	$R_I = 1M\Omega$ $V_I = 0V \dots 1.2V$ (valid range) V_{IH} max = 1.2V	If unused keep line open. The ADC functionality will be available as of Release 2.

Table 2: Signal properties

Function	Signal name	Ю	Signal form and level	Comment
SIM card detection	CCIN	I	$\begin{aligned} R_I &\approx 110 k \Omega \\ V_{IH} \text{min} &= 1.45 \text{V at I} = 15 \mu \text{A}, \\ V_{IH} \text{max} &= 1.9 \text{V} \\ V_{IL} \text{max} &= 0.3 \text{V} \end{aligned}$	CCIN = High, SIM card inserted. For details please refer to Section 2.1.6.
				If unused keep line open.
3V SIM Card Inter- face	CCRST	0	V_{OL} max = 0.30V at I = 1mA V_{OH} min = 2.45V at I = -1mA V_{OH} max = 2.90V	Maximum cable length or copper track to SIM card holder should not exceed 100mm.
	CCIO	I/O	V_{IL} max = 0.50V V_{IH} min = 2.05V V_{IH} max = 2.90V	
			V_{OL} max = 0.25V at I = 1mA V_{OH} min = 2.50V at I = -1mA V_{OH} max = 2.90V	
	CCCLK	0	V_{OL} max = 0.25V at I = 1mA V_{OH} min = 2.40V at I = -1mA V_{OH} max = 2.90V	
	CCVCC	0	V_{O} min = 2.80V V_{O} typ = 2.85V V_{O} max = 2.90V I_{O} max = -30mA	
1.8V SIM Card Inter- face	CCRST	0	V_{OL} max = 0.25V at I = 1mA V_{OH} min = 1.45V at I = -1mA V_{OH} max = 1.90V	
	CCIO	I/O	V_{IL} max = 0.35V V_{IH} min = 1.25V V_{IH} max = 1.85V	
			V_{OL} max = 0.25V at I = 1mA V_{OH} min = 1.50V at I = -1mA V_{OH} max = 1.85V	
	CCCLK	0	V_{OL} max = 0.25V at I = 1mA V_{OH} min = 1.50V at I = -1mA V_{OH} max = 1.85V	
	CCVCC	0	$V_{O}min = 1.75V$ $V_{O}typ = 1.80V$ $V_{O}max = 1.85V$ $I_{O}max = -30mA$	

2.1.2.1 Absolute Maximum Ratings

The absolute maximum ratings stated in Table 3 are stress ratings under any conditions. Stresses beyond any of these limits will cause permanent damage to EHS5-E/EHS5-US.

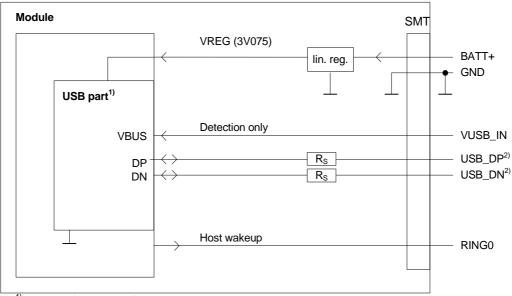
Table 3: Absolute maximum ratings

Parameter	Min	Max	Unit
Supply voltage BATT+ (no service)	-0.3	+5.5	V
Voltage at all digital lines in POWER DOWN mode	-0.3	+0.3	V
Voltage at digital lines in normal operation	-0.2	V180 + 0.2	V
Voltage at SIM/USIM interface, CCVCC in normal operation	0	+3.3	V
VDDLP input voltage	-0.15	2.0	V
Voltage at ADC line in normal operation	0	1.2	V
Voltage at analog lines in POWER DOWN mode	-0.3	+0.3	V
V180 in normal operation	+1.7	+1.9	V
Current at V180 in normal operation		-50	mA
VCORE in normal operation	+0.85	+1.25	V
Current at VCORE in normal operation		-50	mA

2.1.3 USB Interface

EHS5-E/EHS5-US supports a USB 2.0 High Speed (480Mbit/s) device interface that is Full Speed (12Mbit/s) compliant. The USB interface is primarily intended for use as command and data interface and for downloading firmware.

The USB host is responsible for supplying the VUSB_IN line. This line is for voltage detection only. The USB part (driver and transceiver) is supplied by means of BATT+. This is because EHS5-E/EHS5-US is designed as a self-powered device compliant with the "Universal Serial Bus Specification Revision 2.0".



¹⁾ All serial (including R_S) and pull-up resistors for data lines are implemented.

Figure 5: USB circuit

To properly connect the module's USB interface to the host a USB 2.0 compatible connector is required. For more information on the USB related signals see Table 2. Furthermore, the USB modem driver distributed with EHS5-E/EHS5-US needs to be installed.

While the USB connection is active, the module will not change into SLEEP Mode. To enable switching into SLEEP mode the USB host must bring its USB interface into Suspend state. Also, VUSB_IN should always be kept enabled for this functionality. See "Universal Serial Bus Specification Revision 2.0" for a description of the Suspend state. On incoming calls EHS5-E/EHS5-US will then generate a remote wake up request to resume the USB connection (active low).

As an alternative to the regular USB remote wakeup mechanism it is possible to employ the RING0 line to wake up the host application. The benefit is that the RING0 line can wake up the host application in case of incoming calls or other events signalized by URCs while the USB interface is suspended or shut down. For details on this host wakeup interface see Section 2.1.12.3.

²⁾ If the USB interface is operated in High Speed mode (480MHz), it is recommended to take special care routing the data lines USB_DP and USB_DN. Application layout should in this case implement a differential impedance of 90Ohm for proper signal integrity.

^{1.} The specification is ready for download on http://www.usb.org/developers/docs/

2.1.4 Serial Interface ASC0

EHS5-E/EHS5-US offers an 8-wire unbalanced, asynchronous modem interface ASC0 conforming to ITU-T V.24 protocol DCE signalling. The electrical characteristics do not comply with ITU-T V.28. The significant levels are 0V (for low data bit or active state) and 1.8V (for high data bit or inactive state). For electrical characteristics please refer to Table 2. For an illustration of the interface line's startup behavior see Figure 7.

EHS5-E/EHS5-US is designed for use as a DCE. Based on the conventions for DCE-DTE connections it communicates with the customer application (DTE) using the following signals:

- Port TXD @ application sends data to the module's TXD0 signal line
- Port RXD @ application receives data from the module's RXD0 signal line

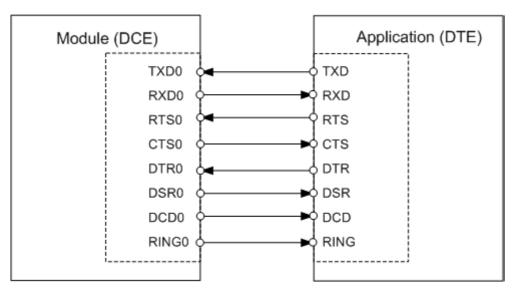
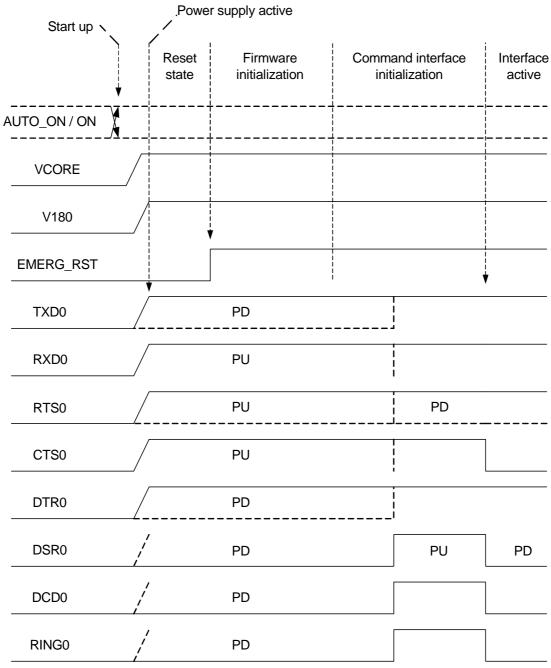


Figure 6: Serial interface ASC0

Features:

- Includes the data lines TXD0 and RXD0, the status lines RTS0 and CTS0 and, in addition, the modem control lines DTR0, DSR0, DCD0 and RING0.
- ASC0 is designed for controlling GSM/UMTS voice calls, transferring data and for controlling the module with AT commands.
- Full multiplexing capability allows the interface to be partitioned into virtual channels.
- The RING0 signal serves to indicate incoming calls and other types of URCs (Unsolicited Result Code). It can also be used to send pulses to the host application, for example to wake up the application from power saving state.
- Configured for 8 data bits, no parity and 1 stop bit.
- ASC0 can be operated at fixed bit rates from 1200bps up to 921600bps.
- Autobauding supports bit rates from 1200bps up to 230400bps.
- Supports RTS0/CTS0 hardware flow control. The hardware hand shake line RTS0 has an
 internal pull down resistor causing a low level signal, if the line is not used and open.
 Although hardware flow control is recommended, this allows communication by using only
 RXD and TXD lines.
- Wake up from SLEEP mode by RTS0 activation (high to low transition).

The following figure shows the startup behavior of the asynchronous serial interface ASC0.



^{*)} For pull-up and pull-down values see Table 11.

Figure 7: ASC0 startup behavior

Please note that during startup the DTR0 signal is driven active low for 500µs. It is recommended to provide a 470 Ohm serial resistor for the DTR0 line to prevent shorts.

Also note that no data must be sent over the ASC0 interface before the interface is active and ready to receive data (see Section 3.2.1.1).

2.1.5 Serial Interface ASC1

EHS5-E/EHS5-US offers a 4-wire unbalanced, asynchronous modem interface ASC1 conforming to ITU-T V.24 protocol DCE signalling. The electrical characteristics do not comply with ITU-T V.28. The significant levels are 0V (for low data bit or active state) and 1.8V (for high data bit or inactive state). For electrical characteristics please refer to Table 2. For an illustration of the interface line's startup behavior see Figure 9.

EHS5-E/EHS5-US is designed for use as a DCE. Based on the conventions for DCE-DTE connections it communicates with the customer application (DTE) using the following signals:

- Port TXD @ application sends data to module's TXD1 signal line
- Port RXD @ application receives data from the module's RXD1 signal line

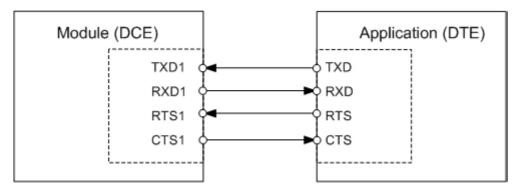
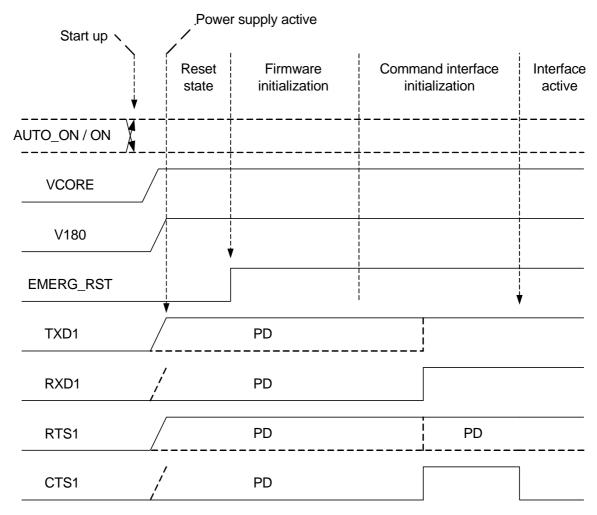


Figure 8: Serial interface ASC1

Features

- Includes only the data lines TXD1 and RXD1 plus RTS1 and CTS1 for hardware handshake.
- On ASC1 no RING line is available.
- Configured for 8 data bits, no parity and 1 or 2 stop bits.
- ASC1 can be operated at fixed bit rates from 1,200 bps to 921600 bps.
- Autobauding supports bit rates from 1200bps up to 230400bps.
- Supports RTS1/CTS1 hardware flow control. The hardware hand shake line RTS1 has an
 internal pull down resistor causing a low level signal, if the line is not used and open.
 Although hardware flow control is recommended, this allows communication by using only
 RXD and TXD lines.

The following figure shows the startup behavior of the asynchronous serial interface ASC1.



^{*)} For pull-down values see Table 11.

Figure 9: ASC1 startup behavior

2.1.6 UICC/SIM/USIM Interface

EHS5-E/EHS5-US has an integrated UICC/SIM/USIM interface compatible with the 3GPP 31.102 and ETSI 102 221. This is wired to the host interface in order to be connected to an external SIM card holder. Five pads on the SMT application interface are reserved for the SIM interface.

The UICC/SIM/USIM interface supports 3V and 1.8V SIM cards. Please refer to Table 2 for electrical specifications of the UICC/SIM/USIM interface lines depending on whether a 3V or 1.8V SIM card is used.

The CCIN signal serves to detect whether a tray (with SIM card) is present in the card holder. Using the CCIN signal is mandatory for compliance with the GSM 11.11 recommendation if the mechanical design of the host application allows the user to remove the SIM card during operation. To take advantage of this feature, an appropriate SIM card detect switch is required on the card holder. For example, this is true for the model supplied by Molex, which has been tested to operate with EHS5-E/EHS5-US and is part of the Cinterion reference equipment submitted for type approval. See Section 7.1 for Molex ordering numbers.

Table 4: Signals of the SIM interface (SMT application interface)

Signal	Description
GND	Separate ground connection for SIM card to improve EMC.
CCCLK	Chipcard clock
CCVCC	SIM supply voltage.
CCIO	Serial data line, input and output.
CCRST	Chipcard reset
CCIN	Input on the baseband processor for detecting a SIM card tray in the holder. If the SIM is removed during operation the SIM interface is shut down immediately to prevent destruction of the SIM. The CCIN signal is by default low and will change to high level if a SIM card is inserted. The CCIN signal is mandatory for applications that allow the user to remove the SIM card during operation. The CCIN signal is solely intended for use with a SIM card. It must not be used for any other purposes. Failure to comply with this requirement may invalidate the type approval of EHS5-E/EHS5-US.

Note: No guarantee can be given, nor any liability accepted, if loss of data is encountered after removing the SIM card during operation. Also, no guarantee can be given for properly initializing any SIM card that the user inserts after having removed the SIM card during operation. In this case, the application must restart EHS5-E/EHS5-US.

The figure below shows a circuit to connect an external SIM card holder.

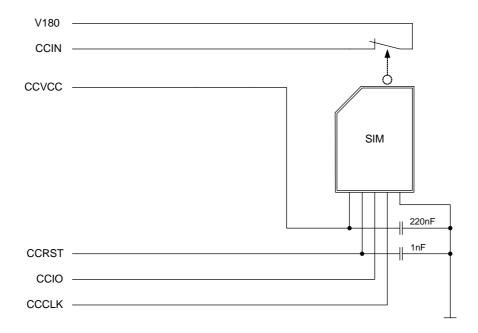


Figure 10: External UICC/SIM/USIM card holder circuit

The total cable length between the SMT application interface pads on EHS5-E/EHS5-US and the pads of the external SIM card holder must not exceed 100mm in order to meet the specifications of 3GPP TS 51.010-1 and to satisfy the requirements of EMC compliance.

To avoid possible cross-talk from the CCCLK signal to the CCIO signal be careful that both lines are not placed closely next to each other. A useful approach is using a GND line to shield the CCIO line from the CCCLK line.

An example for an optimized ESD protection for the SIM interface is shown in Section 2.1.6.1.

2.1.6.1 Enhanced ESD Protection for SIM Interface

To optimize ESD protection for the SIM interface it is possible to add ESD diodes to the SIM interface lines as shown in the example given in Figure 11.

The example was designed to meet ESD protection according ETSI EN 301 489-1/7: Contact discharge: ± 4kV, air discharge: ± 8kV.

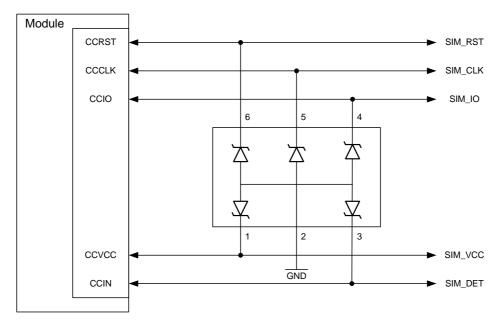


Figure 11: SIM interface - enhanced ESD protection

2.1.7 Digital Audio Interface

EHS5-E/EHS5-US's digital audio interface (DAI) can be used to connect audio devices capable of pulse code modulation (PCM). The PCM functionality allows for the use of an external codec like the MC145483.

The DAI interface supports a 256kHz, long frame synchronization master mode with the following features:

- 16 Bit linear
- 8kHz sample rate
- The most significant bit MSB is transferred first
- 125µs frame duration
- Common frame sync signal for transmit and receive

Table 5 describes the available DAI/PCM lines at the digital audio interface. For electrical details see Section 2.1.2.

Table 5: Overview of DAI/PCM lines

Signal name	Input/Output	Description
TXDDAI	0	PCM data from EHS5-E/EHS5-US to external codec.
RXDDAI	I	PCM data from external codec to EHS5-E/EHS5-US.
TFSDAI	0	Frame synchronization signal to external codec: Long frame @ 256kHz
SCLK	0	Bit clock to external codec: 256kHz

Figure 12 shows the PCM timing for the master mode available with EHS5-E/EHS5-US.

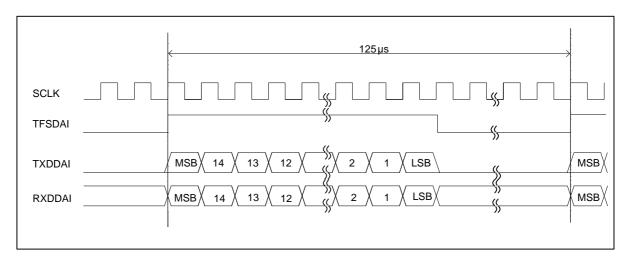


Figure 12: Long frame PCM timing, 256kHz

The following figure shows the start up behaviour of the DAI interface. The start up configuration of functions will be activated after the software initialization of the command interface. With an active state of RING0, CTS0 or CTS1 (low level) the initialization of the DAI interface is finished.

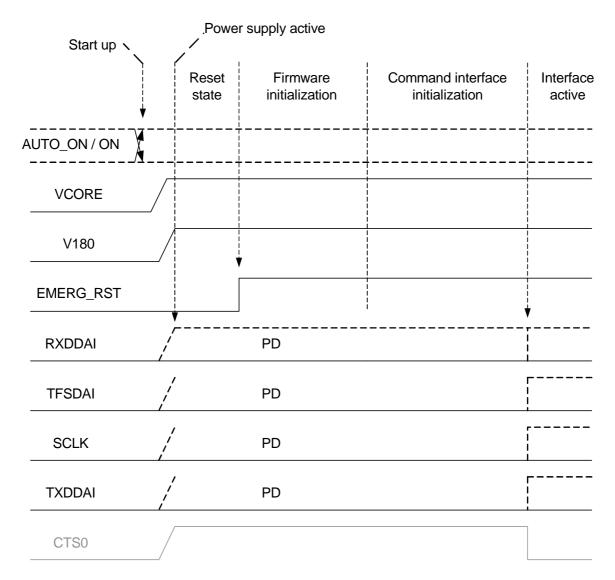


Figure 13: DAI startup timing

2.1.8 RTC Backup

The internal Real Time Clock of EHS5-E/EHS5-US is supplied from a separate voltage regulator in the power supply component which is also active when EHS5-E/EHS5-US is in Power Down mode and BATT+ is available. An alarm function is provided that allows to wake up EHS5-E/EHS5-US without logging on to the GSM/UMTS network.

In addition, you can use the VDDLP pad to backup the RTC from an external capacitor. The capacitor is charged from the internal LDO of EHS5-E/EHS5-US. If the voltage supply at BATT+ is disconnected the RTC can be powered by the capacitor. The size of the capacitor determines the duration of buffering when no voltage is applied to EHS5-E/EHS5-US, i.e. the greater the capacitor the longer EHS5-E/EHS5-US will save the date and time. The RTC can also be supplied from an external battery (rechargeable or non-chargeable). In this case the electrical specification of the VDDLP pad (see Section 2.1.2) has to be taken in to account.

Figure 14 shows an RTC backup configuration. A serial 1kOhm resistor has to be placed on the application next to VDDLP. It limits the input current of an empty capacitor or battery.

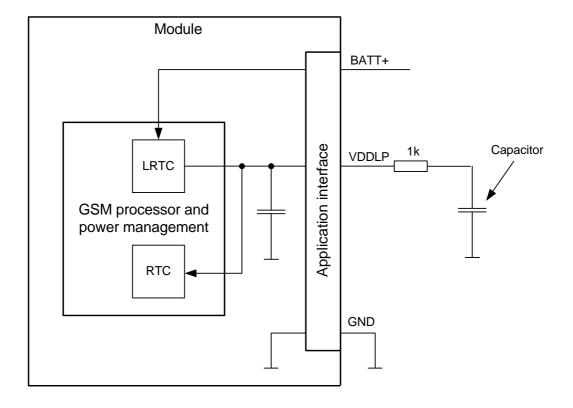


Figure 14: RTC supply variants

2.1.9 **GPIO** Interface

EHS5-E/EHS5-US offers a GPIO interface with 5 GPIO lines¹. The GPIO lines are shared with other interfaces: Status LED (see Section 2.1.12.1) or the PWM functionality (see Section 2.1.11) and the fast shutdown signal (see Section 2.1.12.4).

The following table shows the configuration variants of the GPIO pads. All variants are mutually exclusive, i.e. a pad configured as GPIO is locked for alternative use.

Table 6: GPIO assignment

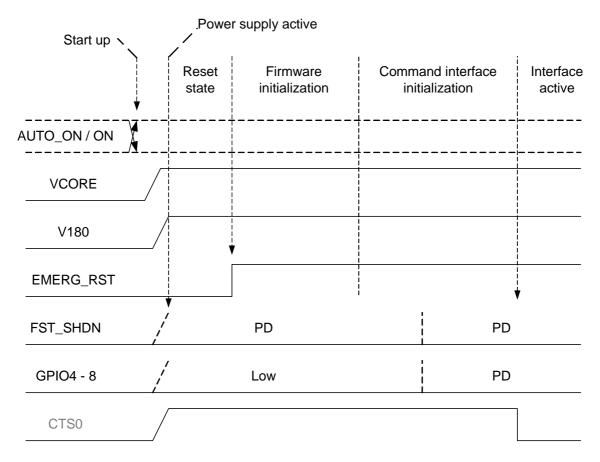
GPIO	PWM	Status LED	Fast Shutdown
GPIO4			FST_SHDN
GPIO5		Status LED	
GPIO6	PWM2		
GPIO7	PWM1		
GPIO8			

When the EHS5-E/EHS5-US starts up, all GPIO lines are set to high-impedance state after initializing, as described in Section 3.2.3. Therefore, it is recommended to connect external pull-up or pull-down resistors to all GPIO lines you want to use as output. This is necessary to keep these lines from floating or driving any external devices.

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^{1.} The GPIO functionality will be available as of Release 2.

The following figure shows the startup behavior of the GPIO interface. With an active state of the ASC0 interface (i.e. RING0, CTS0 or CTS1 are at low level) the initialization of the GPIO interface lines is also finished.



^{*)} For pull down values see Table 11.

Figure 15: GPIO startup behavior

2.1.10 I²C Interface

I²C is a serial, 8-bit oriented data transfer bus for bit rates up to 400kbps in Fast mode¹. It consists of two lines, the serial data line I2CDAT and the serial clock line I2CCLK. The module acts as a single master device, e.g. the clock I2CCLK is driven by the module. I2CDAT is a bi-directional line. Each device connected to the bus is software addressable by a unique 7-bit address, and simple master/slave relationships exist at all times. The module operates as master-transmitter or as master-receiver. The customer application transmits or receives data only on request of the module.

The I²C interface can be powered via the V180 line of EHS5-E/EHS5-US. If connected to the V180 line, the I²C interface will properly shut down when the module enters the Power Down mode.

In the application I2CDAT and I2CCLK lines need to be connected to a positive supply voltage via a pull-up resistor. For electrical characteristics please refer to Table 2.

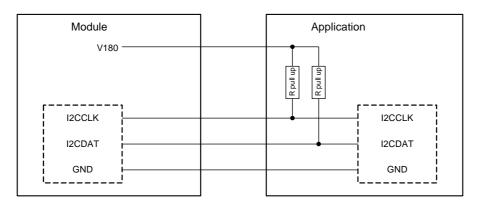


Figure 16: I²C interface connected to V180

Note: Good care should be taken when creating the PCB layout of the host application: The traces of I2CCLK and I2CDAT should be equal in length and as short as possible.

^{1.} The I²C functionality will be available as of Release 2.

The following figure shows the startup behavior of the I²C interface. With an active state of the ASC0 interface (i.e. RING0, CTS0 or CTS1 are at low level) the initialization of the I²C interface is also finished.

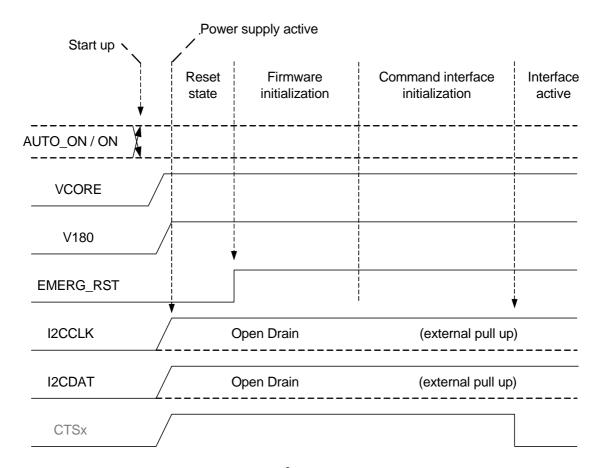


Figure 17: I²C startup behavior

2.1.11 PWM Interfaces

EHS5-E/EHS5-US offers two PWM (Pulse Width Modulation) interfaces, which can be used, for example, to connect buzzers. The PWM1 line is shared with GPIO7 and the PWM2 line is shared with GPIO6 (for GPIOs see Section 2.1.9). GPIO and PWM functionality are mutually exclusive.

The startup behavior of the lines is shown in Figure 15.

2.1.12 Control Signals

2.1.12.1 Status LED

The GPIO5 line at the SMT application interface can be configured to drive a status LED which indicates different operating modes of the module (for GPIOs see Section 2.1.9). GPIO and LED functionality are mutually exclusive.

To take advantage of this function connect an LED to the GPIO5/LED line as shown in Figure 18.

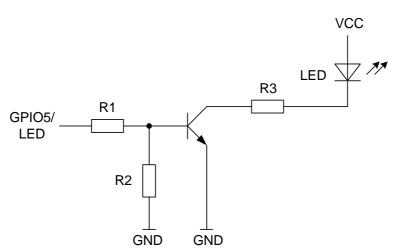


Figure 18: Status signalling with LED driver

2.1.12.2 Power Indication Circuit

In Power Down mode the maximum voltage at any digital or analog interface line must not exceed +0.3V (see also Section 2.1.2.1). Exceeding this limit for any length of time might cause permanent damage to the module.

It is therefore recommended to implement a power indication signal that reports the module's power state and shows whether it is active or in Power Down mode. While the module is in Power Down mode all signals with a high level from an external application need to be set to low state or high impedance state. The sample power indication circuit illustrated in Figure 19 denotes the module's active state with a low signal and the module's Power Down mode with a high signal or high impedance state.

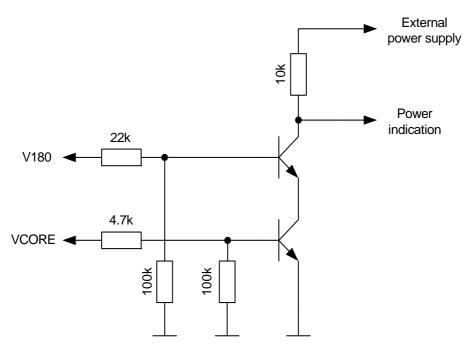


Figure 19: Power indication circuit

2.1.12.3 Host Wakeup

If no call, data or message transfer is in progress, the host may shut down its own USB interface to save power. If a call or other request (URC's, messages) arrives, the host can be notified of these events and be woken up again by a state transition of the ASC0 interface's RING0 line.

Possible RING0 line states are listed in Table 7.

Table 7: Host wakeup lines

Signal	1/0	Description
RING0	0	Inactive to active low transition: 0 = The host shall wake up 1 = No wake up request

2.1.12.4 Fast Shutdown

EHS5-E/EHS5-US provides a fast shutdown signal¹. The GPIO4/FST_SHDN line is an active low control signal and must be applied for at least 10ms. If unused this line can be left open because of a configured internal pull-up resistor. Before setting the GPIO4/FST_SHDN line to low, the ON signal should be set to low (see Figure 20). Otherwise there might be back powering at the ON line in power down mode.

By default, the fast shutdown feature is disabled. It has to be enabled using the AT command AT^SCFG "MEShutdown/Fso". For details see [1].

If enabled, a low impulse >10ms on the GPIO4/FST_SHDN line starts the fast shutdown (see Figure 20). The fast shutdown procedure still finishes any data activities on the module's flash file system, thus ensuring data integrity, but will no longer deregister gracefully from the network, thus saving the time required for network deregistration.

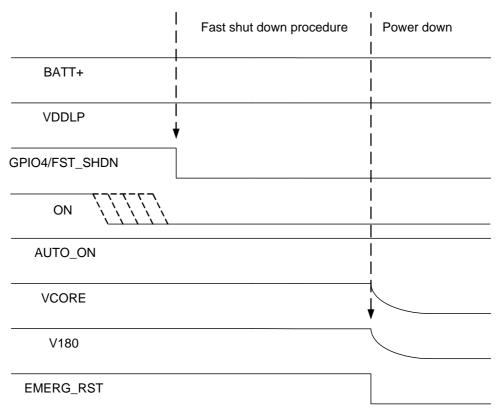


Figure 20: Fast shutdown timing

Please note that if enabled, the normal software controlled shutdown using AT^SMSO will also be a fast shutdown, i.e., without network deregistration. However, in this case no URCs including shutdown URCs will be provided by the AT^SMSO command.

^{1.} The fast shutdown functionality will be available as of Release 2.

2.2 RF Antenna Interface

The RF interface has an impedance of 50Ω . EHS5-E/EHS5-US is capable of sustaining a total mismatch at the antenna line without any damage, even when transmitting at maximum RF power.

The external antenna must be matched properly to achieve best performance regarding radiated power, modulation accuracy and harmonic suppression. Antenna matching networks are not included on the EHS5-E/EHS5-US module and should be placed in the host application if the antenna does not have an impedance of 50Ω .

Regarding the return loss EHS5-E/EHS5-US provides the following values in the active band:

Table 8: Return loss in the active band

State of module	Return loss of module	Recommended return loss of application
Receive	≥ 8dB	≥ 12dB
Transmit	not applicable	≥ 12dB

2.2.1 Antenna Interface Specifications

Table 9: RF Antenna interface GSM / UMTS1

Parameter		Conditions	Min.	Typical	Max.	Unit	
UMTS/HSPA	connectivity	Band I, II, V, VIII	- 1	<u>'</u>		- 1	
Receiver Input ARP	t Sensitivity @	UMTS 850 Band V	-104.7/ -106.7	-110		dBm	
		UMTS 900 Band VIII	-103.7	-110		dBm	
		UMTS 1900 Band II	-104.7	-109		dBm	
		UMTS 2100 Band I	-106.7	-110		dBm	
RF Power @ /	ARP with	UMTS 850 Band V	+21	+24	+25	dBm	
500hm Load Board temperature <85°C		UMTS 900 Band VIII	+21	+24	+25	dBm	
		UMTS 1900 Band II	+21	+24	+25	dBm	
		UMTS 2100 Band I	+21	+24	+25	dBm	
GPRS coding	schemes	Class 12, CS1 to CS4					
EGPRS		Class 12, MCS1 to MCS9					
GSM Class		Small MS					
Static Receive	er input Sensi-	GSM 850 / E-GSM 900	-102	-109		dBm	
tivity @ ARP		GSM 1800 / GSM 1900	-102	-108		dBm	
RF Power @	GSM	GSM 850 / E-GSM 900		33		dBm	
ARP with 50Ohm Load		GSM 1800 / GSM 1900		30		dBm	

Table 9: RF Antenna interface GSM / UMTS¹

Parameter		Conditions	Min.	Typical	Max.	Unit
ARP with 50Ohm Load, (ROPR = 0, i.e. no reduction)	GPRS, 1 TX	GSM 850 / E-GSM 900		33		dBm
		GSM 1800 / GSM 1900		30		dBm
	EDGE, 1 TX	GSM 850 / E-GSM 900		27		dBm
		GSM 1800 / GSM 1900		26		dBm
tion)	GPRS, 2 TX	GSM 1800 / GSM 1900 30 DGE, 2 TX GSM 850 / E-GSM 900 27 GSM 1800 / GSM 1900 26				dBm
		GSM 1800 / GSM 1900		30		dBm
	EDGE, 2 TX	GSM 850 / E-GSM 900		27		dBm
		GSM 1800 / GSM 1900		26		dBm
	GPRS, 3 TX	GSM 850 / E-GSM 900		33		dBm
		GSM 1800 / GSM 1900		30		dBm
	EDGE, 3 TX	GSM 850 / E-GSM 900		27		dBm
		GSM 1800 / GSM 1900		26		dBm
	GPRS, 4 TX	GSM 850 / E-GSM 900		33		dBm
		GSM 1800 / GSM 1900		30		dBm
	EDGE, 4 TX	GSM 850 / E-GSM 900		27		dBm
		GSM 1800 / GSM 1900		26		dBm
RF Power @	GPRS, 1 TX	GSM 850 / E-GSM 900		33		dBm
ARP with 500hm		GSM 1800 / GSM 1900		30		dBm
Load, (ROPR = 1)	EDGE, 1 TX	GSM 850 / E-GSM 900		27		dBm
(KOI K = 1)		GSM 1800 / GSM 1900		26		dBm
	GPRS, 2 TX	GSM 850 / E-GSM 900		33		dBm
		GSM 1800 / GSM 1900		30		dBm
	EDGE, 2 TX	GSM 850 / E-GSM 900		27		dBm
		GSM 1800 / GSM 1900		26		dBm
	GPRS, 3 TX	GSM 850 / E-GSM 900		33		dBm
		GSM 1800 / GSM 1900		30		dBm
	EDGE, 3 TX	GSM 850 / E-GSM 900		27		dBm
		GSM 1800 / GSM 1900		26		dBm
	GPRS, 4 TX	GSM 850 / E-GSM 900		31		dBm
		GSM 1800 / GSM 1900		28		dBm
	EDGE, 4 TX	GSM 850 / E-GSM 900		27		dBm
		GSM 1800 / GSM 1900		26		dBm

Table 9: RF Antenna interface GSM / UMTS¹

Parameter		Conditions	Min.	Typical	Max.	Unit
RF Power @	GPRS, 1 TX	GSM 850 / E-GSM 900		33		dBm
ARP with 500hm		GSM 1800 / GSM 1900		30		dBm
Load, (ROPR = 2)	EDGE, 1 TX	GSM 850 / E-GSM 900		27		dBm
(KOI K = 2)		GSM 850 / E-GSM 900 33 GSM 1800 / GSM 1900 30 GSM 850 / E-GSM 900 27 GSM 1800 / GSM 1900 30 GSM 850 / E-GSM 900 33 GSM 1800 / GSM 1900 30 GSM 850 / E-GSM 900 27 GSM 1800 / GSM 1900 30 GSM 850 / E-GSM 900 27 GSM 1800 / GSM 1900 30 GSM 850 / E-GSM 900 27 GSM 1800 / GSM 1900 30 GSM 850 / E-GSM 900 27 GSM 1800 / GSM 1900 26 GSM 850 / E-GSM 900 27 GSM 1800 / GSM 1900 26 GSM 850 / E-GSM 900 27 GSM 1800 / GSM 1900 26 GSM 850 / E-GSM 900 27 GSM 1800 / GSM 1900 26 GSM 850 / E-GSM 900 27 GSM 1800 / GSM 1900 30 GSM 850 / E-GSM 900 33 GSM 1800 / GSM 1900 30 GSM 850 / E-GSM 900 27 GSM 1800 / GSM 1900 30 GSM 850 / E-GSM 900 27 GSM 1800 / GSM 1900 30 GSM 850 / E-GSM 900 33 GSM 1800 / GSM 1900 30 GSM 850 / E-GSM 900 27 GSM 1800 / GSM 1900 30 GSM 850 / E-GSM 900 27 GSM 1800 / GSM 1900 30 GSM 850 / E-GSM 900 27 GSM 1800 / GSM 1900 30 GSM 850 / E-GSM 900 27 GSM 1800 / GSM 1900 30 GSM 850 / E-GSM 900 27 GSM 1800 / GSM 1900 30 GSM 850 / E-GSM 900 27 GSM 1800 / GSM 1900 30 GSM 850 / E-GSM 900 27 GSM 1800 / GSM 1900 30 GSM 850 / E-GSM 900 27 GSM 1800 / GSM 1900 30 GSM 850 / E-GSM 900 27 GSM 1800 / GSM 1900 30 GSM 850 / E-GSM 900 27 GSM 1800 / GSM 1900 30 GSM 850 / E-GSM 900 27	dBm			
	GPRS, 2 TX	GSM 850 / E-GSM 900		33		dBm
		GSM 1800 / GSM 1900		30		dBm
	EDGE, 2 TX	GSM 850 / E-GSM 900		27		dBm
		GSM 1800 / GSM 1900		26		dBm
	GPRS, 3 TX	GSM 850 / E-GSM 900		33		dBm
		GSM 1800 / GSM 1900		30		dBm
	EDGE, 3 TX	GSM 850 / E-GSM 900		27		dBm
		GSM 1800 / GSM 1900		26		dBm
	GPRS, 4 TX	GSM 850 / E-GSM 900		29		dBm
		GSM 1800 / GSM 1900		26		dBm
	EDGE, 4 TX	GSM 850 / E-GSM 900		27		dBm
		GSM 1800 / GSM 1900		26		dBm
RF Power @	GPRS, 1 TX	GSM 850 / E-GSM 900		33		dBm
ARP with 500hm		GSM 1800 / GSM 1900		30		dBm
Load, (ROPR = 3)	EDGE, 1 TX	GSM 850 / E-GSM 900		27		dBm
(KOI K = 3)		GSM 1800 / GSM 1900		26		dBm
	GPRS, 2 TX	GSM 850 / E-GSM 900		33		dBm
		GSM 1800 / GSM 1900		30		dBm
	EDGE, 2 TX	GSM 850 / E-GSM 900		27		dBm
		GSM 1800 / GSM 1900		26		dBm
	GPRS, 3 TX	GSM 850 / E-GSM 900		33		dBm
		GSM 1800 / GSM 1900		30		dBm
	EDGE, 3 TX	GSM 850 / E-GSM 900		27		dBm
		GSM 1800 / GSM 1900		26		dBm
	GPRS, 4 TX	GSM 850 / E-GSM 900		27		dBm
		GSM 1800 / GSM 1900		24		dBm
	EDGE, 4 TX	GSM 850 / E-GSM 900		27		dBm
		GSM 1800 / GSM 1900		24		dBm

Table 9: RF Antenna interface GSM / UMTS¹

Parameter		Conditions	Min.	Typical	Max.	Unit
RF Power @	GPRS, 1 TX	GSM 850 / E-GSM 900		33		dBm
ARP with 500hm		GSM 1800 / GSM 1900		30		dBm
Load,	EDGE, 1 TX	GSM 850 / E-GSM 900		27		dBm
(ROPR = 4, i.e. maximum		GSM 1800 / GSM 1900		26		dBm
reduction)	GPRS, 2 TX	GSM 850 / E-GSM 900		33		dBm
		GSM 1800 / GSM 1900		30		dBm
	EDGE, 2 TX	GSM 850 / E-GSM 900		27		dBm
		GSM 1800 / GSM 1900		26		dBm
	GPRS, 3 TX	GSM 850 / E-GSM 900		33		dBm
		GSM 1800 / GSM 1900		30		dBm
	EDGE, 3 TX	GSM 850 / E-GSM 900		27		dBm
		GSM 1800 / GSM 1900		26		dBm
	GPRS, 4 TX	GSM 850 / E-GSM 900		27		dBm
		GSM 1800 / GSM 1900		24		dBm
	EDGE, 4 TX	GSM 850 / E-GSM 900		21		dBm
		GSM 1800 / GSM 1900		20		dBm

^{1.} Please note that the listed frequency bands apply as follows:

⁻ EHS5-E: GSM/GPRS 900/1800MHz; UMTS/HSPA+: 900/2100MHz (Band I / VIII)

⁻ EHS5-US: GSM/GPRS: 850/1900MHz; UMTS/HSPA+: 850/1900MHz (Band II / V)

2.2.2 Antenna Installation

The antenna is connected by soldering the antenna pad (RF_OUT, i.e., pad #59) and its neighboring ground pads (GND, i.e., pads #58 and #60) directly to the application's PCB. The antenna pad is the antenna reference point (ARP) for EHS5-E/EHS5-US. All RF data specified throughout this document is related to the ARP.

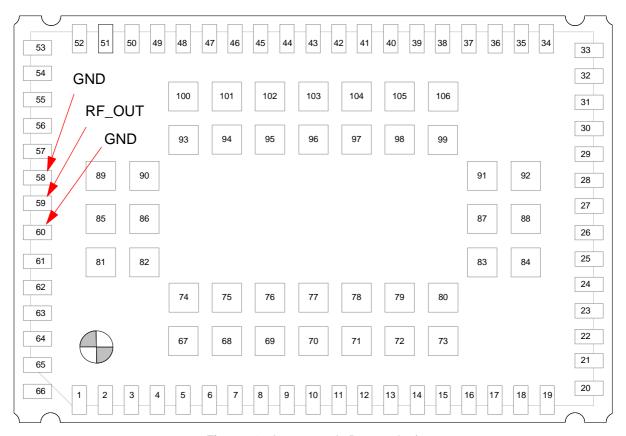


Figure 21: Antenna pads (bottom view)

The distance between the antenna RF_OUT pad (#59) and its neighboring GND pads (#58, #60) has been optimized for best possible impedance. On the application PCB, special attention should be paid to these 3 pads, in order to prevent mismatch.

The wiring of the antenna connection line, starting from the antenna pad to the application antenna should result in a 50Ω line impedance. Line width and distance to the GND plane needs to be optimized with regard to the PCB's layer stack. Some examples are given in Section 2.2.3.

To prevent receiver desensitization due to interferences generated by fast transients like high speed clocks on the application PCB, it is recommended to realize the antenna connection line using embedded Stripline rather than Micro-Stripline technology. Please see Section 2.2.3.1 for an example.

For type approval purposes, the use of a 50Ω coaxial antenna connector (U.FL-R-SMT) might be necessary. In this case the U.FL-R-SMT connector should be placed as close as possible to EHS5-E/EHS5-US's antenna pad.

2.2.3 RF Line Routing Design

2.2.3.1 Line Arrangement Examples

Several dedicated tools are available to calculate line arrangements for specific applications and PCB materials - for example from http://www.polarinstruments.com/ (commercial software) or from http://web.awrcorp.com/Usa/Products/Optional-Products/TX-Line/ (free software).

Embedded Stripline

This figure below shows a line arrangement example for embedded stripline with 65µm FR4 prepreg (type: 1080) and 710µm FR4 core (4-layer PCB).

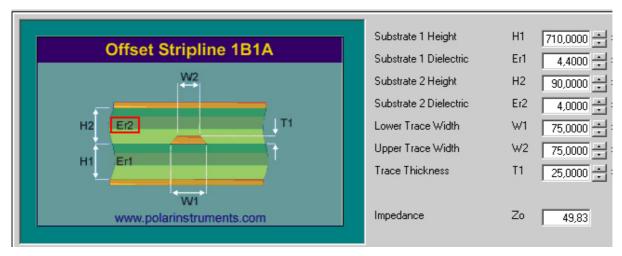


Figure 22: Embedded Stripline with 65µm prepreg (1080) and 710µm core

Micro-Stripline

This section gives two line arrangement examples for micro-stripline.

Micro-Stripline on 1.0mm Standard FR4 2-Layer PCB
 The following two figures show examples with different values for D1 (ground strip separation).



Figure 23: Micro-Stripline on 1.0mm standard FR4 2-layer PCB - example 1

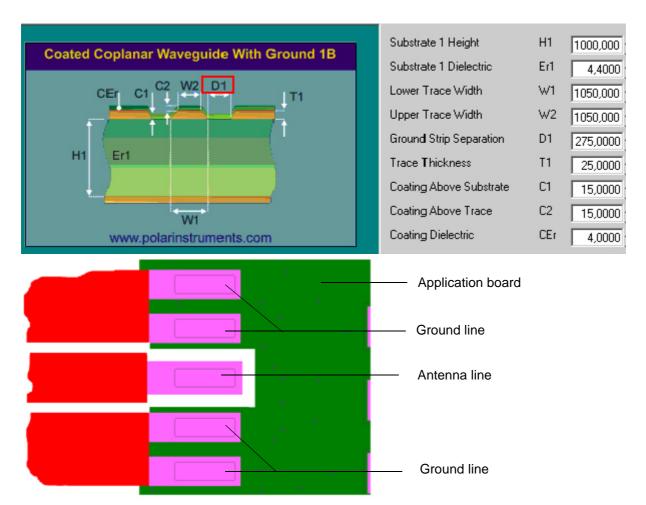


Figure 24: Micro-Stripline on 1.0mm Standard FR4 PCB - example 2

Micro-Stripline on 1.5mm Standard FR4 2-Layer PCB
 The following two figures show examples with different values for D1 (ground strip separation).



Figure 25: Micro-Stripline on 1.5mm Standard FR4 PCB - example 1

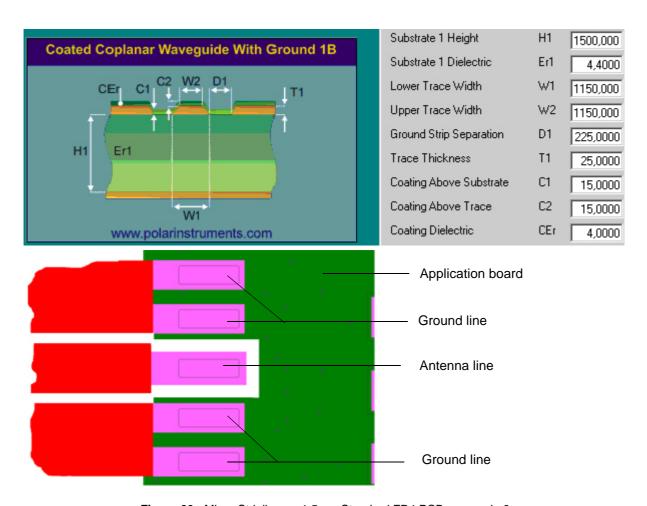


Figure 26: Micro-Stripline on 1.5mm Standard FR4 PCB - example 2

2.2.3.2 Routing Example

Interface to RF Connector

Figure 27 shows the connection of the module's antenna pad with an application PCB's coaxial antenna connector. Please note that the EHS5-E/EHS5-US bottom plane appears mirrored, since it is viewed from EHS5-E/EHS5-US top side. By definition the top of customer's board shall mate with the bottom of the EHS5-E/EHS5-US module.

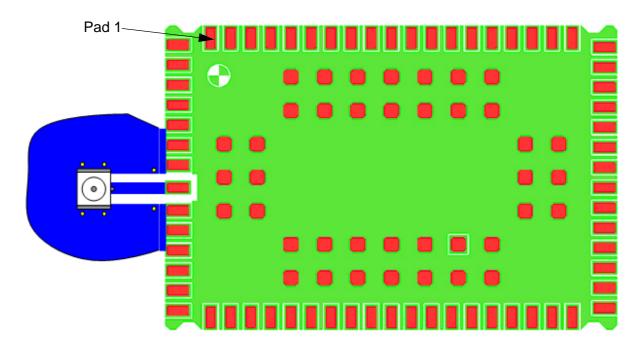


Figure 27: Routing to application's RF connector - top view

2.3 Sample Application

Figure 28 shows a typical example of how to integrate a EHS5-E/EHS5-US module with an application. Usage of the various host interfaces depends on the desired features of the application.

Because of the very low power consumption design, current flowing from any other source into the module circuit must be avoided, for example reverse current from high state external control lines. Therefore, the controlling application must be designed to prevent reverse current flow. Otherwise there is the risk of undefined states of the module during startup and shutdown or even of damaging the module.

Because of the high RF field density inside the module, it cannot be guaranteed that no self interference might occur, depending on frequency and the applications grounding concept. excluded that in some applications dependant on the grounding concept of the customer. The potential interferers may be minimized by placing small capacitors (47pF) at suspected lines (e.g. RXD0, VDDLP, and ON).

While developing SMT applications it is strongly recommended to provide test points for certain signals resp. lines to and from the module - for debug and/or test purposes. The SMT application should allow for an easy access to these signals. For details on how to implement test points see [4].

The EMC measures are best practice recommendations. In fact, an adequate EMC strategy for an individual application is very much determined by the overall layout and, especially, the position of components. For example, mounting the internal acoustic transducers directly on the PCB eliminates the need to use the ferrite beads shown in the sample schematic.

Please note that EHS5-E/EHS5-US is not intended for use with cables longer than 3m.

Disclaimer

No warranty, either stated or implied, is provided on the sample schematic diagram shown in Figure 28 and the information detailed in this section. As functionality and compliance with national regulations depend to a great amount on the used electronic components and the individual application layout manufacturers are required to ensure adequate design and operating safeguards for their products using EHS5-E/EHS5-US modules.

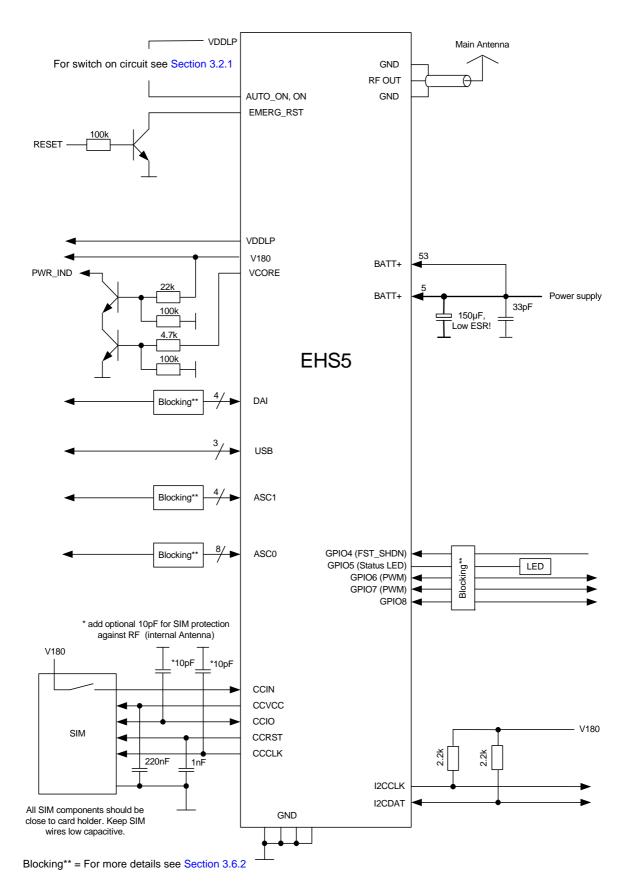


Figure 28: Schematic diagram of EHS5-E/EHS5-US sample application

3 Operating Characteristics

3.1 Operating Modes

The table below briefly summarizes the various operating modes referred to throughout the document.

Table 10: Overview of operating modes

Mode	Function				
Normal operation	GSM / GPRS / UMTS / HSPA SLEEP	No call is in progress and the USB connection is suspended by host (or is not present) and no active communication via ASC0. For power saving issues see Section 3.3.			
	GSM / GPRS / UMTS / HSPA IDLE	No call is in progress and the USB connection is not suspended by host (or is not present) and no active communication via ASC0. For power saving issues see Section 3.3.			
	GSM TALK/ GSM DATA	Connection between two subscribers is in progress. Power consumption depends on the GSM network coverage and several connection settings (e.g. DTX off/on, FR/EFR/HR, hopping sequences and antenna connection). The following applies when power is to be measured in TALK_GSM mode: DTX off, FR and no frequency hopping.			
	GPRS DATA	GPRS data transfer in progress. Power consumption depends on network settings (e.g. power control level), uplink / downlink data rates and GPRS configuration (e.g. used multislot settings).			
	EGPRS DATA	EGPRS data transfer in progress. Power consumption depends on network settings (e.g. power control level), uplink / downlink data rates and EGPRS configuration (e.g. used multislot settings).			
	UMTS TALK/ UMTS DATA	UMTS data transfer in progress. Power consumption depends on network settings (e.g. TPC Pattern) and data transfer rate.			
	HSPA DATA	HSPA data transfer in progress. Power consumption depends on network settings (e.g. TPC Pattern) and data transfer rate.			
Power Down	The second control of the property of the second control of the se				
Airplane mode	Airplane mode shuts down the radio part of the module, causes the module to log off from the GSM/GPRS network and disables all AT commands whose execution requires a radio connection. Airplane mode can be controlled by AT command (see [1]).				

3.2 Power Up/Power Down Scenarios

In general, be sure not to turn on EHS5-E/EHS5-US while it is beyond the safety limits of voltage and temperature stated in Section 2.1.2.1. EHS5-E/EHS5-US would immediately switch off after having started and detected these inappropriate conditions. In extreme cases this can cause permanent damage to the module.

3.2.1 Turn on EHS5-E/EHS5-US

EHS5-E/EHS5-US can be started as described in the following sections:

- Hardware driven switch on by (continuous) AUTO_ON line: Starts Normal mode (see Section 3.2.1.1 and Section 3.2.1.2). It is recommended to employ the AUTO_ON line as module startup signal.
- Hardware driven switch on by ON line: Starts Normal mode (see Section 3.2.1.3)

After startup or restart, the module will send the URC ^SYSSTART that notifies the host application that the first AT command can be sent to the module (see also [1]).

3.2.1.1 Switch on EHS5-E/EHS5-US Using AUTO_ON Signal

When the operating voltage BATT+ is applied, EHS5-E/EHS5-US can also be switched on by means of the AUTO_ON signal.

The AUTO_ON signal is a low level sensitive signal and only allows the input voltage level of the VDDLP signal. The module starts into normal mode with AUTO_ON at a continuously low level. Please note that BATT+ should already be active and stable before the low level at the AUTO_ON signal is applied.

The following Figure 29 shows an example for a switch-on circuit, Figure 30 shows the AUTO ON signal timing.

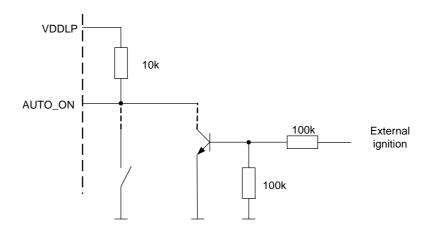


Figure 29: AUTO_ON circuit sample

It is recommended to use a 10k Ohm pull up resistor at the AUTO_ON pad. The 10kOhm pull up resistor may be required in an electrically noisy environment.

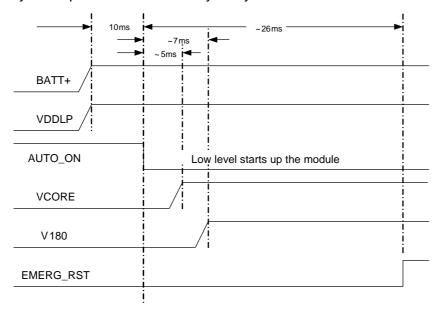


Figure 30: AUTO_ON signal timing

3.2.1.2 Switch on EHS5-E/EHS5-US Using a Continuous AUTO_ON Signal

In case the AUTO_ON signal is permanently connected to ground (i.e., low level) the module will start up if the operating voltage BATT+ is applied with a rise time of less than 1ms between 2.5V to 3.2V.

The following Figure 31 shows this startup behavior if employing the AUTO_ON signal.

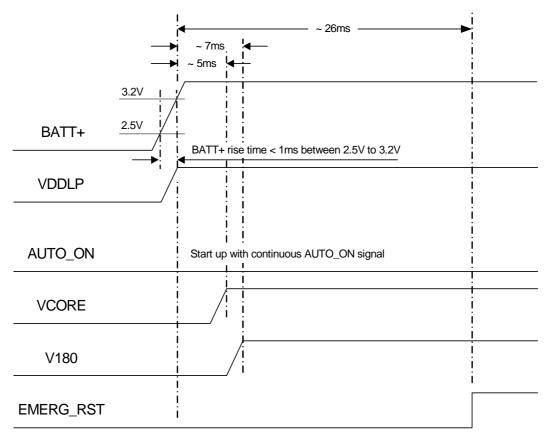


Figure 31: AUTO_ON timing

3.2.1.3 Switch on EHS5-E/EHS5-US Using ON Signal

When the operating voltage BATT+ is applied, EHS5-E/EHS5-US can also be switched on by means of the ON signal.

The ON signal is a level, i.e., high pulse triggered signal and only allows the input voltage level of the VDDLP signal. The module starts into normal mode on detecting a high pulse at the ON signal. The high pulse width should be between a minimum of 50µs and a maximum of 80µs.

The following Figure 32 shows recommendations for a possible switch-on circuit.

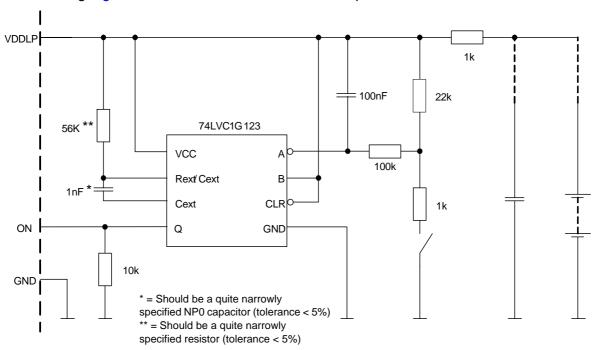


Figure 32: ON circuit options

It is recommended to set a serial 1kOhm resistor between the ON circuit and the external capacitor or battery at the VDDLP power supply. This serial resistor protection is necessary in case the capacitor or battery has low power (is empty).

The above ON circuit with the monostable multivibrator 74LVC1G123 as component generates a high pulse with a pulse width of typically 60µs.

Please note that BATT+ and VDDLP should be active at least 10ms before the high pulse at the ON signal is applied to start up the module. After module startup the ON signal should always be set to low to prevent possible back powering at this line.

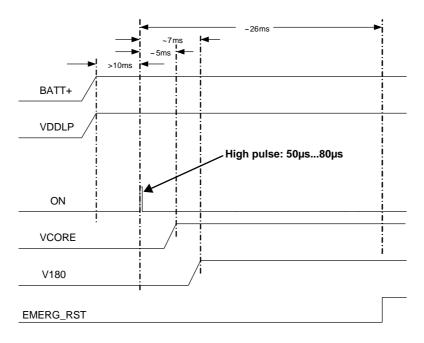


Figure 33: ON timing

3.2.2 Restart EHS5-E/EHS5-US

After startup EHS5-E/EHS5-US can be re-started as described in the following sections:

- Software controlled reset by AT+CFUN command: Starts Normal mode (see Section 3.2.2.1).
- Hardware controlled reset by EMERG_RST line: Starts Normal mode (see Section 3.2.2.2)

3.2.2.1 Restart EHS5-E/EHS5-US via AT+CFUN Command

To reset and restart the EHS5-E/EHS5-US module use the command AT+CFUN. See [1] for details.

3.2.2.2 Restart EHS5-E/EHS5-US Using EMERG_RST

The EMERG_RST signal is internally connected to the central GSM processor. A low level for more than 10ms sets the processor and with it all the other signal pads to their respective reset state. The reset state is described in Section 3.2.3 as well as in the figures showing the startup behavior of an interface.

After releasing the EMERG-RST line, i.e., with a change of the signal level from low to high, the module restarts. The other signals continue from their reset state as if the module was switched on by the ON or AUTO_ON signal.

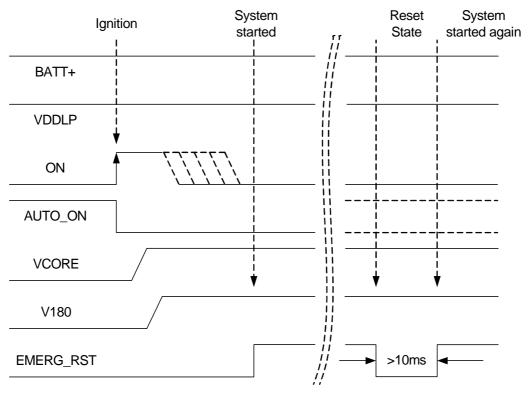


Figure 34: Emergency restart timing

It is recommended to control this EMERG_RST line with an open collector transistor or an open drain field-effect transistor.

Caution: Use the EMERG_RST line only when, due to serious problems, the software is not responding for more than 5 seconds. Pulling the EMERG_RST line causes the loss of all information stored in the volatile memory. Therefore, this procedure is intended only for use in case of emergency, e.g. if EHS5-E/EHS5-US does not respond, if reset or shutdown via AT command fails.

3.2.3 Signal States after Startup

Table 11 lists the states each interface signal passes through during reset and firmware initialization.

The reset state is reached with the rising edge of the EMERG_RST signal - either after a normal module startup (see Section 3.2.1.1) or after a reset (see Section 3.2.2.2). After the reset state has been reached the firmware initialization state begins. The firmware initialization is completed as soon as the ASC0 interface lines CTS0, DSR0 and RING0 as well as the ASC1 interface line CTS1 have turned low (see Section 2.1.4 and Section 2.1.5). Now, the module is ready to receive and transmit data.

Table 11: Signal states

Reset state	Firmware initialization
T/PD	I / 100k PD
L	O/L
L	O/L
L	O/L
T/PU	O/H
T/PD	1
T/PU	O/H
T/PU	I/PD
T/PD	O/H
T/PD	I
T/PD	O/H
T/PD	O/H
T/PD	O/H
T/PD	I
T/PD	O/H
T/PD	I/PD
T/PD	O/L
T/PD	I
T/PD	O/L
T/PD	O/L
T/PD	T/PD
O/L	T/PD
Т	T/OD
Т	T/OD
	T/PD L L L L T/PU T/PD T/PD T/PU T/PD T/PD T/PD T/PD T/PD T/PD T/PD T/PD

Abbreviations used in above Table 11:

L = Low level	I = Input
H = High level	O = Output
L/H = Low or high level	OD = Open Drain
T = Tristate	PD = Pull down, 200µA at 1.9V
	PU = Pull up, -240µA at 0V

3.2.4 Turn off EHS5-E/EHS5-US

To switch the module off the following procedures may be used:

- Software controlled shutdown procedure: Software controlled by sending an AT command over the serial application interface. See Section 3.2.4.1.
- Hardware controlled shutdown procedure: Hardware controlled by disconnecting the module's power supply lines BATT+. See Section 3.2.4.2.
- Automatic shutdown (software controlled): See Section 3.2.5
 - Takes effect if EHS5-E/EHS5-US board temperature exceeds a critical limit.

3.2.4.1 Switch off EHS5-E/EHS5-US Using AT Command

The best and safest approach to powering down EHS5-E/EHS5-US is to issue the appropriate AT command. This procedure lets EHS5-E/EHS5-US log off from the network and allows the software to enter into a secure state and safe data before disconnecting the power supply. The mode is referred to as Power Down mode. In this mode, only the RTC stays active. Before issueing the switch off AT command, the ON signal should be set to low (see Figure 35). Otherwise there might be back powering at the ON line in power down mode.

Be sure not to disconnect the operating voltage $V_{BATT_{+}}$ before V180 pad has gone low. Otherwise you run the risk of losing data.

While EHS5-E/EHS5-US is in Power Down mode the application interface is switched off and must not be fed from any other voltage source. Therefore, your application must be designed to avoid any current flow into any digital pads of the application interface.

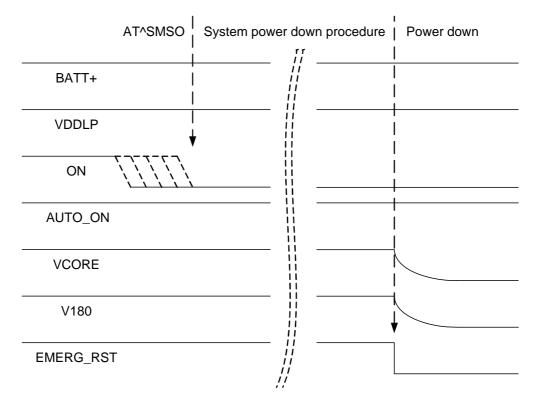


Figure 35: Switch off behavior

3.2.4.2 Disconnect EHS5-E/EHS5-US BATT+ Lines

Figure 36 shows an external application circuit that provides the possibility to temporarily (>100ms) disconnect the module's BATT+ lines from the external application's power supply. The mentioned MOSFET transistor (T8) should have an R_{DS_ON} value ≤ 50 mOhm in order to minimize voltage drops. Such a circuit could be useful to maximize power savings for battery driven applications or to completely switch off and restart the module after a firmware update.

Afterwards the module can be restarted as described in Section 3.2.1.

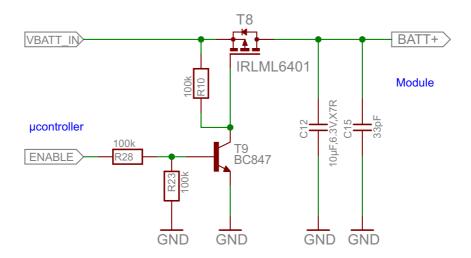


Figure 36: Restart circuit using BATT+ line

3.2.5 Automatic Shutdown

Automatic shutdown takes effect if the following event occurs:

 The EHS5-E/EHS5-US board is exceeding the critical limits of overtemperature or undertemperature

The automatic shutdown procedure is equivalent to the power-down initiated with an AT command, i.e. EHS5-E/EHS5-US logs off from the network and the software enters a secure state avoiding loss of data.

3.2.5.1 Thermal Shutdown

The board temperature is constantly monitored by an internal NTC resistor located on the PCB. The values detected by the NTC resistor are measured directly on the board and therefore, are not fully identical with the ambient temperature.

Each time the board temperature goes out of range or back to normal, EHS5-E/EHS5-US instantly displays an alert (if enabled).

- URCs indicating the level "1" or "-1" allow the user to take appropriate precautions, such as
 protecting the module from exposure to extreme conditions. The presentation of the URCs
 depends on the settings selected with the AT^SCTM write command (for details see [1]):
 AT^SCTM=1: Presentation of URCs is always enabled.
 - AT^SCTM=0 (default): Presentation of URCs is disabled, i.e. no URCs with alert levels "1" or "-1" will be generated.
- URCs indicating the level "2" or "-2" are instantly followed by an orderly shutdown. The presentation of these URCs is always enabled, i.e. they will be output even though the factory setting AT^SCTM=0 was never changed.

The maximum temperature ratings are stated in Section 5.2. Refer to Table 12 for the associated URCs.

Table 12: Temperature dependent behavior

Sending tempera	Sending temperature alert (only if URC presentation enabled)					
^SCTM_B: 1	Board close to overtemperature limit.					
^SCTM_B: -1	Board close to undertemperature limit.					
^SCTM_B: 0	Board back to non-critical temperature range.					
Automatic shutd	own (URC appears no matter whether or not presentation was enabled)					
^SCTM_B: 2	Alert: Board equal or beyond overtemperature limit. EHS5-E/EHS5-US switches off.					
^SCTM_B: -2	Alert: Board equal or below undertemperature limit. EHS5-E/EHS5-US switches off.					

3.3 Power Saving

EHS5-E/EHS5-US can be configured in two ways to control power consumption:

 Using the AT command AT^SPOW it is possible to specify a so-called power saving mode for the module (<mode> = 2; for details on the command see [1]). The module's UART interfaces (ASC0 and ASC1) are then deactivated and will only periodically be activated to be able to listen to network paging messages as described in Section 3.3.1 and Section 3.3.2.

Please note that the AT^SPOW setting has no effect on the USB interface. As long as the USB connection is active, the module will not change into its SLEEP state to reduce its functionality to a minimum and thus minimizing its current consumption. To enable switching into SLEEP mode, the USB connection must therefore either not be present at all or the USB host must bring its USB interface into Suspend state. Also, VUSB_IN should always be kept enabled for this functionality. See "Universal Serial Bus Specification Revision 2.0" for a description of the Suspend state.

 Using the AT command AT^SCFG="Radio/OutputPowerReduction" it is possible for the module in GPRS and EGPRS multislot scenarios to reduce its output power according to 3GPP 45.005 section. By default a maximum power reduction is enabled. For details on the command see [1].

3.3.1 Power Saving while Attached to GSM Networks

The power saving possibilities while attached to a GSM network depend on the paging timing cycle of the base station. The duration of a power saving interval can be calculated using the following formula:

t = 4.615 ms (TDMA frame duration) * 51 (number of frames) * DRX value.

DRX (Discontinuous Reception) is a value from 2 to 9, resulting in paging intervals between 0.47 and 2.12 seconds. The DRX value of the base station is assigned by the GSM network operator.

In the pauses between listening to paging messages, the module resumes power saving, as shown in Figure 37.



Figure 37: Power saving and paging in GSM networks

^{1.} The specification is ready for download on http://www.usb.org/developers/docs/

The varying pauses explain the different potential for power saving. The longer the pause the less power is consumed.

Generally, power saving depends on the module's application scenario and may differ from the above mentioned normal operation. The power saving interval may be shorter than 0.47 seconds or longer than 2.12 seconds.

3.3.2 Power Saving while Attached to WCDMA Networks

The power saving possibilities while attached to a WCDMA network depend on the paging timing cycle of the base station.

During normal WCDMA operation, i.e., the module is connected to a WCDMA network, the duration of a power saving period varies. It may be calculated using the following formula:

 $t = 2^{DRX \text{ value}} * 10 \text{ ms}$ (WCDMA frame duration).

DRX (Discontinuous Reception) in WCDMA networks is a value between 6 and 9, thus resulting in power saving intervals between 0.64 and 5.12 seconds. The DRX value of the base station is assigned by the WCDMA network operator.

In the pauses between listening to paging messages, the module resumes power saving, as shown in Figure 38.

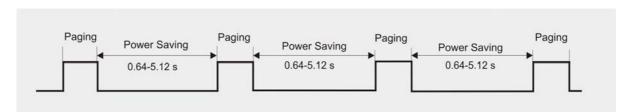


Figure 38: Power saving and paging in WCDMA networks

The varying pauses explain the different potential for power saving. The longer the pause the less power is consumed.

Generally, power saving depends on the module's application scenario and may differ from the above mentioned normal operation. The power saving interval may be shorter than 0.64 seconds or longer than 5.12 seconds.

3.4 Power Supply

EHS5-E/EHS5-US needs to be connected to a power supply at the SMT application interface (2 lines each BATT+ and GND).

The power supply of EHS5-E/EHS5-US has to be a single voltage source at BATT+. It must be able to provide the peak current during the uplink transmission.

All the key functions for supplying power to the device are handled by the power management section of the analog controller. This IC provides the following features:

- Stabilizes the supply voltages for the baseband using low drop linear voltage regulators and a DC-DC step down switching regulator.
- Switches the module's power voltages for the power-up and -down procedures.
- SIM switch to provide SIM power supply.

3.4.1 Power Supply Ratings

Table 13: Power supply ratings¹

	Description	Conditions		Min	Тур	Max	Unit
BATT+	Voltage must stay within the min/max values, including voltage drop, ripple, spikes Maximum allowed voltage drop during transmit burst Voltage must stay within the min/max values, including voltage drop, ripple, spikes		3.3	3.8	4.5	V	
					400	mV	
	Voltage ripple	Normal condition, power Pout max @ f <= 250 kHz @ f > 250 kHz	@ f <= 250 kHz			190 30	${ m mV}_{ m pp}$ ${ m mV}_{ m pp}$
I _{VDDLP} @ 1.8V	OFF State supply current	TC backup @ BATT+ = 0V			<1		μΑ
I _{BATT+} ²	OFF State supply current	POWER DOWN			60		μΑ
	Average GSM /	SLEEP ³ @ DRX=9	USB disconnected		0.9 1.1 1.1	mA	
	GPRS supply cur- rent	(UART deactivated)	EP ³ @ DRX=5 RT deactivated) USB suspended USB suspended USB suspended		1.1		mA
	Toric	SLEEP ³ @ DRX=5	USB disconnected		1.1		mA
	USB suspended	USB suspended		1.3		mA	
		SLEEP ³ @ DRX=2 (UART deactivated)	USB disconnected		1.4		mA
			USB suspended		1.6		mA
		IDLE @ DRX=2 (UART activated, but no communication)	USB disconnected		14		mA
		IDLE @ DRX=2 (UART activated, but no communication)	USB suspend		36		mA
		Voice Call GSM850/900); PCL=5		245		mA
		GPRS Data transfer GSM850/900; PCL=5; 1Tx/4Rx	ROPR=4 (max. reduction)		240		mA
			ROPR=0 (no reduction)				
		GPRS Data transfer GSM850/900; PCL=5;	ROPR=4 (max. reduction)		310		mA
		2Tx/3Rx	ROPR=0 (no reduction)		430		mA
		GPRS Data transfer GSM850/900; PCL=5;	ROPR=4 (max. reduction)		330		mA
		4Tx/1Rx	ROPR=0 (no reduction)		790		mA
		EDGE Data transfer GSM850/900; PCL=5;	ROPR=4 (max. reduction)		170		mA
		1Tx/4Rx	ROPR=0 (no reduction)				

Table 13: Power supply ratings¹

	Description	Conditions		Min	Тур	Max	Unit
I _{BATT+} ²	Average GSM / GPRS supply	EDGE Data transfer GSM850/900; PCL=5;	ROPR=4 (max. reduction)		230		mA
	Average GSM / GPRS supply current EDG GSM 4Tx/3 Voice GPR GSM PCL= GPR GSM PCL= EDG GSM PCL=	2Tx/3Rx	ROPR=0 (no reduction)		295		mA
		EDGE Data transfer GSM850/900; PCL=5; 4Tx/1Rx ROPR=0 (no reduction reductio	ROPR=4 (max. reduction)		360		mA
		4Tx/1Rx	ROPR=0 (no reduction)		515		mA
		Voice Call GSM1800/19	900; PCL=0		180		mA
ĺ		GSM1800/1900;	ROPR=4 (max. reduction)		180		mA
		PCL=0; 11x/4Rx	ROPR=0 (no reduction)				
		GPRS Data transfer GSM1800/1900;	ROPR=4 (max. reduction)		200		mA
		PCL=0; 2Tx/3Rx	ROPR=0 (no reduction)		310		mA
		GPRS Data transfer GSM1800/1900;	ROPR=4 (max. reduction)		240		mA
		PCL=0; 4Tx/1Rx	ROPR=0 (no reduction)		550		mA
		EDGE Data transfer GSM1800/1900;	ROPR=4 (max. reduction)		150		mA
		PCL=0; 1Tx/4Rx	ROPR=0 (no reduction)				
		EDGE Data transfer GSM1800/1900;	ROPR=4 (max. reduction)		220		mA
		PCL=0; 2Tx/3Rx	ROPR=0 (no reduction)		250		mA
		EDGE Data transfer GSM1800/1900;	ROPR=4 (max. reduction)		350		mA
		PCL=0; 4Tx/1Rx	ROPR=0 (no reduction)		430		mA
		VOICE Call GSM850/90	00; PCL=5		1.6	2.3	Α
	ing GSM transmit burst	VOICE Call GSM1800/	1900; PCL=0		1.1		А

Table 13: Power supply ratings¹

	Description	Conditions		Min	Тур	Max	Unit
I _{BATT+} 2 I _{BATT+} 2	Average WCDMA supply current Average WCDMA supply current	SLEEP ³ @ DRX=9 (UART deactivated)	USB disconnected		1.2		mA
			USB suspended		1.4		mA
		SLEEP ³ @ DRX=8 (UART deactivated)	USB disconnected		1.2		mA
			USB suspended		1.4		mA
		SLEEP ³ @ DRX=6 (UART deactivated)	USB disconnected		1.8		mA
			USB suspended		2.0		mA
		IDLE @ DRX=6 (UART activated, but no communication)	USB disconnected		13		mA
		IDLE @ DRX=6 (UART activated, but no communication)	USB suspend		35		mA
		Voice Call Band I; 24dBm			520		mA
		Voice Call Band II; 24dBm			560		mA
		Voice Call Band V; 24dBm			460		mA
		Voice Call Band VIII; 24dBm			530		mA
		UMTS Data transfer Band I @+24dBm			440		mA
		UMTS Data transfer Band II @+24dBm			490		mA
		UMTS Data transfer Band V @+24dBm			410		mA
		UMTS Data transfer Band VIII @+24dBm			470		mA
		HSPA Data transfer Band I @+24dBm			440		mA
		HSPA Data transfer Band II @+24dBm			490		mA
HSPA Data transfer Band V @+24c			nd V @+24dBm		410		mA
		HSPA Data transfer Band VIII @+24dBm			470		mA

- 1. Please note that the listed frequency bands apply as follows:
 - EHS5-E: GSM/GPRS 900/1800MHz; UMTS/HSPA+: 900/2100MHz (Band I / VIII)
 - EHS5-US: GSM/GPRS: 850/1900MHz; UMTS/HSPA+: 850/1900MHz (Band II / V
- 2. With an impedance of Z_{LOAD} =500hm at the antenna connector.
- 3. Measurements start 6 minutes after switching on the module,

Averaging times: SLEEP mode - 3 minutes, transfer modes - 1.5 minutes

Communication tester settings: no neighbour cells, no cell reselection etc., RMC (reference measurement channel)

SLEEP mode (power saving) is enabled by means of the AT command AT^SPOW=2,1000,3

3.4.2 Minimizing Power Losses

When designing the power supply for your application please pay specific attention to power losses. Ensure that the input voltage V_{BATT+} never drops below 3.3V on the EHS5-E/EHS5-US board, not even in a GSM transmit burst where current consumption can rise (for peaks values see the power supply ratings listed in Section 3.4.1). It should be noted that EHS5-E/EHS5-US switches off when exceeding these limits. Any voltage drops that may occur in a transmit burst should not exceed 400mV.

The module switches off if the minimum battery voltage (V_{BattMin}) is reached.

$$\begin{split} &\text{Example:} \\ &\text{V}_{\text{BattLowLimit}} = 3.3 \text{V} \\ &\text{D}_{\text{DropMax}} = 0.4 \text{V} \\ &\text{V}_{\text{BattMin}} = \text{V}_{\text{BattLowLimit}} + \text{D}_{\text{DropMax}} \\ &\text{V}_{\text{BattMin}} = 3.3 \text{V} + 0.4 \text{V} = 3.7 \text{V} \end{split}$$

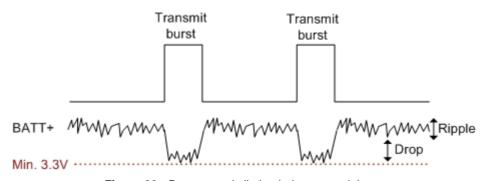


Figure 39: Power supply limits during transmit burst

3.4.3 Measuring the Supply Voltage (V_{BATT+})

To measure the supply voltage V_{BATT+} it is possible to define two reference points GND and BATT+. GND should be the module's shielding, while BATT+ should be a test pad on the external application the module is mounted on. The external BATT+ reference point has to be connected to and positioned close to the SMT application interface's BATT+ pads 5 or 53 as shown in Figure 40.

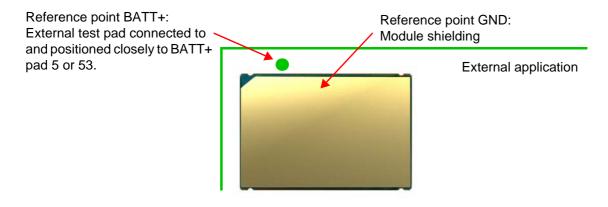


Figure 40: Position of reference points BATT+and GND

3.5 Operating Temperatures

Please note that the module's lifetime, i.e., the MTTF (mean time to failure) may be reduced, if operated outside the extended temperature range.

Table 14: Board temperature

Parameter	Min	Тур	Max	Unit
Normal operation	-30	+25	+85	°C
Extended operation ¹	-40		+90	°C
Automatic shutdown ² Temperature measured on EHS5-E/EHS5-US board	<-40		>+90	°C

^{1.} Extended operation allows normal mode speech calls or data transmission for limited time until automatic thermal shutdown takes effect. Within the extended temperature range (outside the normal operating temperature range) the specified electrical characteristics may be in- or decreased.

See also Section 3.2.5 for information about the NTC for on-board temperature measurement, automatic thermal shutdown and alert messages.

Note that within the specified operating temperature ranges the board temperature may vary to a great extent depending on operating mode, used frequency band, radio output power and current supply voltage.

For more information regarding the module's thermal behavior please refer to [3].

^{2.} Due to temperature measurement uncertainty, a tolerance of ±3°C on the thresholds may occur.

3.6 Electrostatic Discharge

The GSM module is not protected against Electrostatic Discharge (ESD) in general. Consequently, it is subject to ESD handling precautions that typically apply to ESD sensitive components. Proper ESD handling and packaging procedures must be applied throughout the processing, handling and operation of any application that incorporates a EHS5-E/EHS5-US module.

An example for an enhanced ESD protection for the SIM interface is given in Section 2.1.6.1.

EHS5-E/EHS5-US has been tested according to group standard ETSI EN 301 489-1 (see Table 22) and test standard EN 61000-4-2. Electrostatic values can be gathered from the following table.

Table 15: Electrostatic values

Specification/Requirements	Contact discharge	Air discharge					
EN 61000-4-2							
Antenna interface	± 1kV	n.a.					
Antenna interface with ESD protection (see Section 3.6.1)	± 4kV	± 8kV					
JEDEC JESD22-A114D (Human Body Model, Test conditions: 1.5 kΩ, 100 pF)							
All other interfaces	± 1kV	n.a.					

Note: Please note that the values may vary with the individual application design. For example, it matters whether or not the application platform is grounded over external devices like a computer or other equipment, such as the Cinterion reference application described in Chapter 5.

3.6.1 ESD Protection for Antenna Interface

The following Figure 41 shows how to implement an external ESD protection for the RF antenna interface with either a T pad or PI pad attenuator circuit (for RF line routing design see also Section 2.2.3).

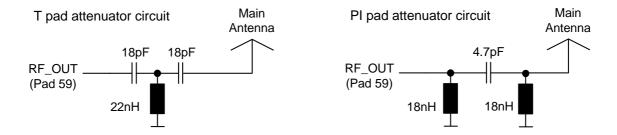


Figure 41: ESD protection for RF antenna interface

Recommended inductor types for the above sample circuits: Size 0402 SMD from Panasonic ELJRF series (22nH and 18nH inductors) or Murata LQW15AN18NJ00 (18nH inductors only).

3.6.2 Blocking against RF on Interface Lines

To reduce EMI issues there are serial resistors, or capacitors to GND, implemented on the module for the ignition, emergency restart, and SIM interface lines (cp. Section 2.3). However, all other signal lines have no EMI measures on the module and there are no blocking measures at the module's interface to an external application.

Dependent on the specific application design, it might be useful to implement further EMI measures on some signal lines at the interface between module and application. These measures are described below.

There are five possible variants of EMI measures (A-E) that may be implemented between module and external application depending on the signal line (see Figure 42 and Table 16). Pay attention not to exceed the maximum input voltages and prevent voltage overshots if using inductive EMC measures.

The maximum value of the serial resistor should be lower than 1kOhm on the signal line. The maximum value of the capacitor should be lower than 50pF on the signal line. Please observe the electrical specification of the module's SMT application interface and the external application's interface.

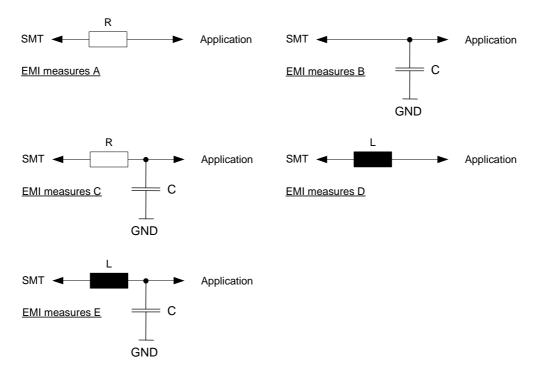


Figure 42: EMI circuits

The following table lists for each signal line at the module's SMT application interface the EMI measures that may be implemented.

Table 16: EMI measures on the application interface

Signal name	EMI measures					Remark	
	Α	В	С	D	E		
CCIN	х			х			
CCRST		х				The external capacitor should be not higher	
CCIO		х				than 30pF. The value of the capacitor depends on the external application.	
CCCLK		х					
RXD0	Х	х	х	х	х		
TXD0	Х	х	х	х	х		
CTS0	Х	х	х	х	х		
RTS0				х			
RING0				х			
DTR0	х	х	х	х	х		
DCD0	х	х	х	х	х		
DSR0	х	х	х	х	х		
RXD1	х	х	х	х	х		
TXD1	Х	х	х	х	х		
CTS1	Х	х	х	х	х		
RTS1	х	х	х	х	х		
GPIO4/FST_SHDN	х	х	х	х	х		
GPIO5/LED	х	х	х	х	х		
GPIO6/PWM2	х	х	х	х	х		
GPIO7/PWM1	х	х	х	х	х		
GPIO8	Х	х	х	х	х		
I2CDAT		х		х		The rising signal edge is reduced with an	
I2CCLK		х		х		additional capacitor.	
V180		х		х	х		
VCORE		Х		Х	Х		

3.7 Reliability Characteristics

The test conditions stated below are an extract of the complete test specifications.

Table 17: Summary of reliability test conditions

Type of test	Conditions	Standard
Vibration	Frequency range: 10-20Hz; acceleration: 5g Frequency range: 20-500Hz; acceleration: 20g Duration: 20h per axis; 3 axes	DIN IEC 60068-2-6 ¹
Shock half-sinus	Acceleration: 500g Shock duration: 1msec 1 shock per axis 6 positions (± x, y and z)	DIN IEC 60068-2-27
Dry heat	Temperature: +70 ±2°C Test duration: 16h Humidity in the test chamber: < 50%	EN 60068-2-2 Bb ETS 300 019-2-7
Temperature change (shock)	Low temperature: -40°C ±2°C High temperature: +85°C ±2°C Changeover time: < 30s (dual chamber system) Test duration: 1h Number of repetitions: 100	DIN IEC 60068-2-14 Na ETS 300 019-2-7
Damp heat cyclic	High temperature: +55°C ±2°C Low temperature: +25°C ±2°C Humidity: 93% ±3% Number of repetitions: 6 Test duration: 12h + 12h	DIN IEC 60068-2-30 Db ETS 300 019-2-5
Cold (constant exposure)	Temperature: -40 ±2°C Test duration: 16h	DIN IEC 60068-2-1

^{1.} For reliability tests in the frequency range 20-500Hz the Standard's acceleration reference value was increased to 20g.

4 Mechanical Dimensions, Mounting and Packaging

The following sections describe the mechanical dimensions of EHS5-E/EHS5-US and give recommendations for integrating EHS5-E/EHS5-US into the host application. Additional information can be found in a number of files containing Gerber data for the external application footprint and product model data in STEP format. These data are zipped in an extra file package supplied along with the EHS5-E/EHS5-US documentation package. To open these files commonly used Gerber and STEP viewers may be employed. The file package is named ehs5_gerber_stp_v01.7z.

4.1 Mechanical Dimensions of EHS5-E/EHS5-US

Figure 43 shows the top and bottom view of EHS5-E/EHS5-US and provides an overview of the board's mechanical dimensions. For further details see Figure 44.

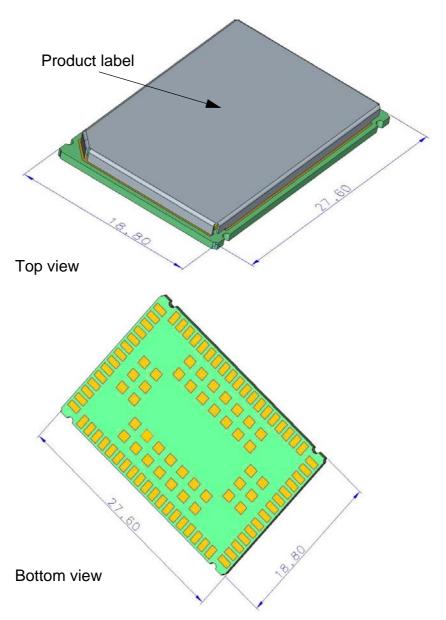


Figure 43: EHS5-E/EHS5-US- top and bottom view

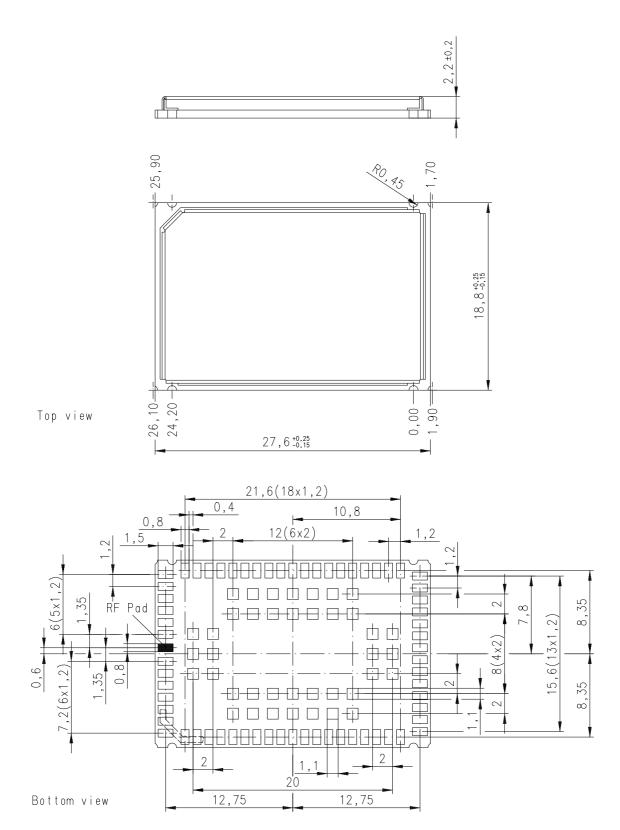


Figure 44: Dimensions of EHS5-E/EHS5-US (all dimensions in mm)

4.2 Mounting EHS5-E/EHS5-US onto the Application Platform

This section describes how to mount EHS5-E/EHS5-US onto the PCBs (=printed circuit boards), including land pattern and stencil design, board-level characterization, soldering conditions, durability and mechanical handling. For more information on issues related to SMT module integration see also [4].

Note: To avoid short circuits between signal tracks on an external application's PCB and various markings at the bottom side of the module, it is recommended not to route the signal tracks on the top layer of an external PCB directly under the module, or at least to ensure that signal track routes are sufficiently covered with solder resist.

4.2.1 SMT PCB Assembly

4.2.1.1 Land Pattern and Stencil

The land pattern and stencil design as shown below is based on Cinterion characterizations for lead-free solder paste on a four-layer test PCB and a 110 respectively 150 micron thick stencil.

The land pattern given in Figure 45 reflects the module's pad layout, including signal pads and ground pads (for pad assignment see Section 2.1.1).

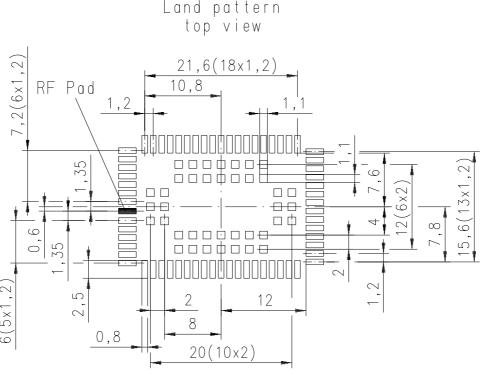


Figure 45: Land pattern (top view)

The stencil design illustrated in Figure 46 and Figure 47 is recommended by Cinterion as a result of extensive tests with Cinterion Daisy Chain modules.

The central ground pads are primarily intended for stabilizing purposes, and may show some more voids than the application interface pads at the module's rim. This is acceptable, since they are electrically irrelevant.

Note that depending on coplanarity or other properties of the external PCB, it could be that all of the central ground pads may have to be soldered. For this reason the land pattern design shown in Figure 45 provides for both of these alternatives and only a modification of the stencil may be needed.

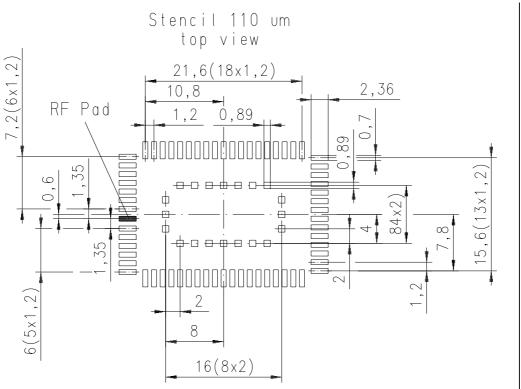


Figure 46: Recommended design for 110 micron thick stencil (top view)

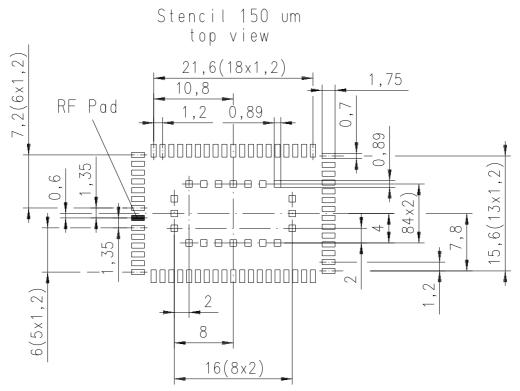


Figure 47: Recommended design for 150 micron thick stencil (top view)

4.2.1.2 Board Level Characterization

Board level characterization issues should also be taken into account if devising an SMT process.

Characterization tests should attempt to optimize the SMT process with regard to board level reliability. This can be done by performing the following physical tests on sample boards: Peel test, bend test, tensile pull test, drop shock test and temperature cycling. Sample surface mount checks are described in [4].

It is recommended to characterize land patterns before an actual PCB production, taking individual processes, materials, equipment, stencil design, and reflow profile into account. For land and stencil pattern design recommendations see also Section 4.2.1.1. Optimizing the solder stencil pattern design and print process is necessary to ensure print uniformity, to decrease solder voids, and to increase board level reliability.

Daisy chain modules for SMT characterization are available on request. For details refer to [4].

Generally, solder paste manufacturer recommendations for screen printing process parameters and reflow profile conditions should be followed. Maximum ratings are described in Section 4.2.3.

4.2.2 Moisture Sensitivity Level

EHS5-E/EHS5-US comprises components that are susceptible to damage induced by absorbed moisture.

Cinterion's EHS5-E/EHS5-US module complies with the latest revision of the IPC/JEDEC J-STD-020 Standard for moisture sensitive surface mount devices and is classified as MSL 4.

For additional MSL (=moisture sensitivity level) related information see Section 4.2.4 and Section 4.3.2.

4.2.3 Soldering Conditions and Temperature

4.2.3.1 Reflow Profile

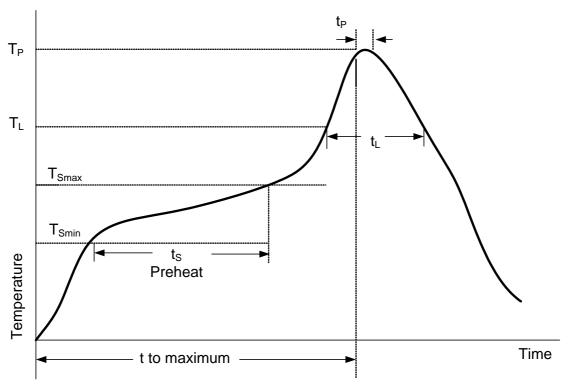


Figure 48: Reflow Profile

Table 18: Reflow temperature ratings

Profile Feature	Pb-Free Assembly
	150°C 200°C 60-120 seconds
Average ramp up rate (T _{Smax} to T _P)	3K/second max.
Liquidous temperature (T _L) Time at liquidous (t _L)	217°C 60-90 seconds
Peak package body temperature (T _P)	245°C +0/-5°C
Time (t_P) within 5 °C of the peak package body temperature (T_P)	30 seconds max.
Average ramp-down rate (T _P to T _{Smax})	6 K/second max.
Time 25°C to maximum temperature	8 minutes max.

4.2.3.2 Maximum Temperature and Duration

The following limits are recommended for the SMT board-level soldering process to attach the module:

- A maximum module temperature of 245°C. This specifies the temperature as measured at the module's top side.
- A maximum duration of 30 seconds at this temperature.

Please note that while the solder paste manufacturers' recommendations for best temperature and duration for solder reflow should generally be followed, the limits listed above must not be exceeded.

EHS5-E/EHS5-US is specified for one soldering cycle only. Once EHS5-US is removed from the application, the module will very likely be destroyed and cannot be soldered onto another application.

4.2.4 Durability and Mechanical Handling

4.2.4.1 Storage Conditions

EHS5-E/EHS5-US modules, as delivered in tape and reel carriers, must be stored in sealed, moisture barrier anti-static bags. The conditions stated below are only valid for modules in their original packed state in weather protected, non-temperature-controlled storage locations. Normal storage time under these conditions is 12 months maximum.

Table 19: Storage conditions

Туре	Condition	Unit	Reference
Air temperature: Low High	-25 +40	°C	IPC/JEDEC J-STD-033A
Humidity relative: Low High	10 90 at 40°C	%	IPC/JEDEC J-STD-033A
Air pressure: Low High	70 106	kPa	IEC TR 60271-3-1: 1K4 IEC TR 60271-3-1: 1K4
Movement of surrounding air	1.0	m/s	IEC TR 60271-3-1: 1K4
Water: rain, dripping, icing and frosting	Not allowed		
Radiation: Solar Heat	1120 600	W/m ²	ETS 300 019-2-1: T1.2, IEC 60068-2-2 Bb ETS 300 019-2-1: T1.2, IEC 60068-2-2 Bb
Chemically active substances	Not recommended		IEC TR 60271-3-1: 1C1L
Mechanically active substances	Not recommended		IEC TR 60271-3-1: 1S1
Vibration sinusoidal: Displacement Acceleration Frequency range	1.5 5 2-9 9-200	mm m/s ² Hz	IEC TR 60271-3-1: 1M2
Shocks: Shock spectrum Duration Acceleration	semi-sinusoidal 1 50	ms m/s ²	IEC 60068-2-27 Ea

4.2.4.2 Processing Life

EHS5-E/EHS5-US must be soldered to an application within 72 hours after opening the MBB (=moisture barrier bag) it was stored in.

As specified in the IPC/JEDEC J-STD-033 Standard, the manufacturing site processing the modules should have ambient temperatures below 30°C and a relative humidity below 60%.

4.2.4.3 **Baking**

Baking conditions are specified on the moisture sensitivity label attached to each MBB (see Figure 53 for details):

- It is *not necessary* to bake EHS5-E/EHS5-US, if the conditions specified in Section 4.2.4.1 and Section 4.2.4.2 were not exceeded.
- It is *necessary* to bake EHS5-E/EHS5-US, if any condition specified in Section 4.2.4.1 and Section 4.2.4.2 was exceeded.

If baking is necessary, the modules must be put into trays that can be baked to at least 125°C. Devices should not be baked in tape and reel carriers at any temperature.

4.2.4.4 Electrostatic Discharge

ESD (=electrostatic discharge) may lead to irreversable damage for the module. It is therefore advisable to develop measures and methods to counter ESD and to use these to control the electrostatic environment at manufacturing sites.

Please refer to Section 3.6 for further information on electrostatic discharge.

4.3 Packaging

4.3.1 Tape and Reel

The single-feed tape carrier for EHS5-E/EHS5-US is illustrated in Figure 49. The figure also shows the proper part orientation. The tape width is 44 mm and the EHS5-US modules are placed on the tape with a 28-mm pitch. The reels are 330 mm in diameter with a core diameter of 100 mm. Each reel contains 500 modules.

4.3.1.1 Orientation

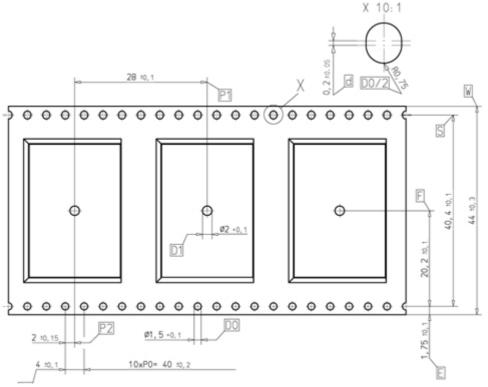


Figure 49: Carrier tape

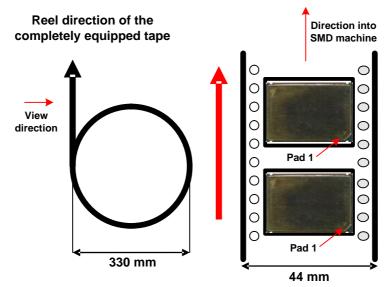


Figure 50: Reel direction

4.3.1.2 Barcode Label

A barcode label provides detailed information on the tape and its contents. It is attached to the reel.

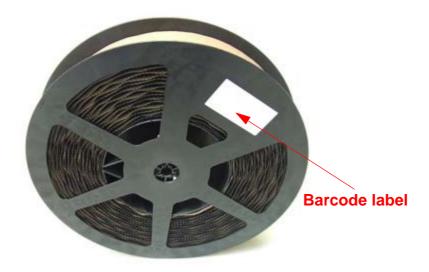


Figure 51: Barcode label on tape reel

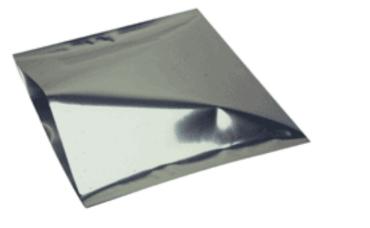
4.3.2 Shipping Materials

EHS5-E/EHS5-US is distributed in tape and reel carriers. The tape and reel carriers used to distribute EHS5-E/EHS5-US are packed as described below, including the following required shipping materials:

- Moisture barrier bag, including desiccant and humidity indicator card
- Transportation box

4.3.2.1 Moisture Barrier Bag

The tape reels are stored inside an MBB (=moisture barrier bag), together with a humidity indicator card and desiccant pouches - see Figure 52. The bag is ESD protected and delimits moisture transmission. It is vacuum-sealed and should be handled carefully to avoid puncturing or tearing. The bag protects the EHS5-E/EHS5-US modules from moisture exposure. It should not be opened until the devices are ready to be soldered onto the application.



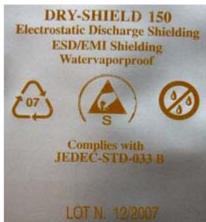


Figure 52: Moisture barrier bag (MBB) with imprint

The label shown in Figure 53 summarizes requirements regarding moisture sensitivity, including shelf life and baking requirements. It is attached to the outside of the moisture barrier bag.

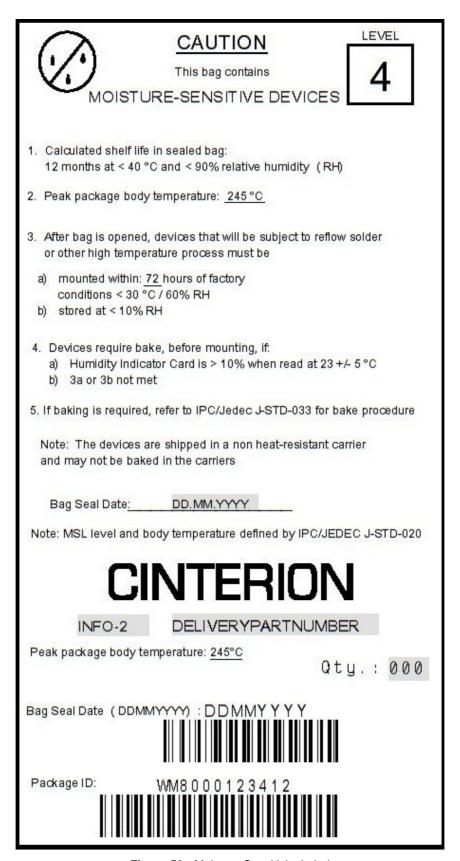


Figure 53: Moisture Sensitivity Label

MBBs contain one or more desiccant pouches to absorb moisture that may be in the bag. The humidity indicator card described below should be used to determine whether the enclosed components have absorbed an excessive amount of moisture.

The desiccant pouches should not be baked or reused once removed from the MBB.

The humidity indicator card is a moisture indicator and is included in the MBB to show the approximate relative humidity level within the bag. Sample humidity cards are shown in Figure 54. If the components have been exposed to moisture above the recommended limits, the units will have to be rebaked.

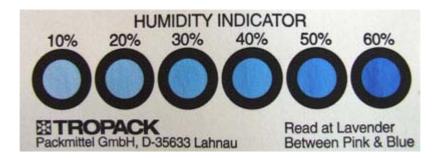


Figure 54: Humidity Indicator Card - HIC

A baking is required if the humidity indicator inside the bag indicates 10% RH or more.

4.3.2.2 Transportation Box

Tape and reel carriers are distributed in a box, marked with a barcode label for identification purposes. A box contains two reels with 500 modules each.

4.3.3 Trays

If small module quantities are required, e.g., for test and evaluation purposes, EHS5-E/EHS5-US may be distributed in trays (for dimensions see Figure 58). The small quantity trays are an alternative to the single-feed tape carriers normally used. However, the trays are not designed for machine processing. They contain modules to be (hand) soldered onto an external application (for information on hand soldering see [4]).

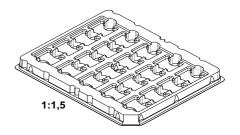


Figure 55: Small quantity tray

Trays are packed and shipped in the same way as tape carriers, including a moisture barrier bag with desiccant and humidity indicator card as well as a transportation box (see also Section 4.3.2).



Figure 56: Tray to ship odd module amounts



Figure 57: Trays with packaging materials

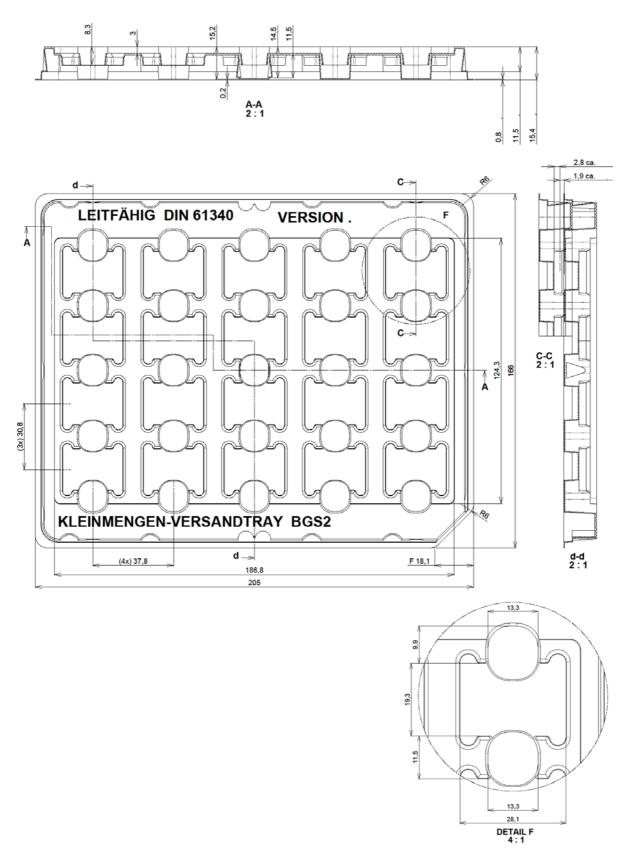


Figure 58: Tray dimensions

5 Regulatory and Type Approval Information

5.1 Directives and Standards

EHS5-E/EHS5-US is designed to comply with the directives and standards listed below.

It is the responsibility of the application manufacturer to ensure compliance of the final product with all provisions of the applicable directives and standards as well as with the technical specifications provided in the "EHS5-E/EHS5-US Hardware Interface Description".

Table 20: Directives

1999/05/EC	Directive of the European Parliament and of the council of 9 March 1999 on radio equipment and telecommunications terminal equipment and the mutual recognition of their conformity (in short referred to as R&TTE Directive 1999/5/EC). The product is labeled with the CE conformity mark C € 0682
2002/95/EC	Directive of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS)

Table 21: Standards of North American type approval¹

CFR Title 47	Code of Federal Regulations, Part 22 and Part 24 (Telecommunications, PCS); US Equipment Authorization FCC
OET Bulletin 65 (Edition 97-01)	Evaluating Compliance with FCC Guidelines for Human Exposure to Radiofrequency Electromagnetic Fields
UL 60 950-1	Product Safety Certification (Safety requirements)
NAPRD.03 V5.13	Overview of PCS Type certification review board Mobile Equipment Type Certification and IMEI control PCS Type Certification Review board (PTCRB)
RSS132 (Issue2) RSS133 (Issue5)	Canadian Standard

^{1.} Applies to the module variant EHS5-US only.

Table 22: Standards of European type approval¹

3GPP TS 51.010-1	Digital cellular telecommunications system (Release 7); Mobile Station (MS) conformance specification;
ETSI EN 301 511 V9.0.2	Global System for Mobile communications (GSM); Harmonized standard for mobile stations in the GSM 900 and DCS 1800 bands covering essential requirements under article 3.2 of the R&TTE directive (1999/5/EC)
GCF-CC V3.47	Global Certification Forum - Certification Criteria

^{1.} Manufacturers of applications which can be used in the US shall ensure that their applications have a PTCRB approval. For this purpose they can refer to the PTCRB approval of the respective module.

Table 22: Standards of European type approval¹

ETSI EN 301 489-01 V1.8.1	Electromagnetic Compatibility and Radio spectrum Matters (ERM); Electromagnetic Compatibility (EMC) standard for radio equipment and services; Part 1: Common Technical Requirements
ETSI EN 301 489-07 V1.3.1	Electromagnetic Compatibility and Radio spectrum Matters (ERM); Electromagnetic Compatibility (EMC) standard for radio equipment and services; Part 7: Specific conditions for mobile and portable radio and ancillary equipment of digital cellular radio telecommunications systems (GSM and DCS)
ETSI EN 301 489-24 V1.5.1	Electromagnetic Compatibility and Radio spectrum Matters (ERM); Electromagnetic Compatibility (EMC) standard for radio equipment and services; Part 24: Specific conditions for IMT-2000 CDMA Direct Spread (UTRA) for Mobile and portable (UE) radio and ancillary equipment
ETSI EN 301 908-01 V5.2.1	Electromagnetic compatibility and Radio spectrum Matters (ERM); Base Stations (BS) and User Equipment (UE) for IMT-2000 Third Generation cellular networks; Part 1: Harmonized EN for IMT-2000, introduction and common requirements of article 3.2 of the R&TTE Directive
ETSI EN 301 908-02 V5.2.1	Electromagnetic compatibility and Radio spectrum Matters (ERM); Base Stations (BS) and User Equipment (UE) for IMT-2000 Third Generation cellular networks; Part 2: Harmonized EN for IMT-2000, CDMA Direct Spread (UTRA FDD) (UE) covering essential requirements of article 3.2 of the R&TTE Directive
EN 62311:2008	Assessment of electronic and electrical equipment related to human exposure restrictions for electromagnetic fields (0 Hz - 300 GHz)
EN 60950-1:2006+ A11:2009+A1:2010 IEC 60950-1:2005/ A1:2009 (second edition)	Safety of information technology equipment

^{1.} Applies to the module variant EHS5-E only.

Table 23: Requirements of quality

IEC 60068	Environmental testing	
DIN EN 60529	IP codes	

Table 24: Standards of the Ministry of Information Industry of the People's Republic of China

SJ/T 11363-2006	"Requirements for Concentration Limits for Certain Hazardous Substances in Electronic Information Products" (2006-06).
SJ/T 11364-2006	"Marking for Control of Pollution Caused by Electronic Information Products" (2006-06).
	According to the "Chinese Administration on the Control of Pollution caused by Electronic Information Products" (ACPEIP) the EPUP, i.e., Environmental Protection Use Period, of this product is 20 years as per the symbol shown here, unless otherwise marked. The EPUP is valid only as long as the product is operated within the operating limits described in the Cinterion Wireless Modules Hardware Interface Description. Please see Table 25 for an overview of toxic or hazardous substances or elements that might be contained in product parts in concentrations above the limits defined by SJ/T 11363-2006.

Table 25: Toxic or hazardous substances or elements with defined concentration limits

部件名称	有毒有害物质或元素 Hazardous substances						
Name of the part	铅 (Pb)	汞 (Hg)	镉 (Cd)	六价铬 (Cr(VI))	多溴联苯 (PBB)	多溴二苯醚 (PBDE)	
金属部件 (Metal Parts)	0	0	0	0	0	0	
电路模块 (Circuit Modules)	х	0	0	0	0	0	
电缆及电缆组件 (Cables and Cable Assemblies)	0	0	0	0	0	0	
塑料和聚合物部件 (Plastic and Polymeric parts)	0	0	0	0	0	0	

0:

表示该有毒有害物质在该部件所有均质材料中的含量均在SJ/T11363-2006 标准规定的限量要求以下。 Indicates that this toxic or hazardous substance contained in all of the homogeneous materials for this part is below the limit requirement in SJ/T11363-2006.

X:

表示该有毒有害物质至少在该部件的某一均质材料中的含量超出SJ/T11363-2006标准规定的限量要求。 Indicates that this toxic or hazardous substance contained in at least one of the homogeneous materials used for this part *might exceed* the limit requirement in SJ/T11363-2006.

5.2 SAR requirements specific to portable mobiles

Mobile phones, PDAs or other portable transmitters and receivers incorporating a GSM module must be in accordance with the guidelines for human exposure to radio frequency energy. This requires the Specific Absorption Rate (SAR) of portable EHS5-E/EHS5-US based applications to be evaluated and approved for compliance with national and/or international regulations.

Since the SAR value varies significantly with the individual product design manufacturers are advised to submit their product for approval if designed for portable use. For European and US markets the relevant directives are mentioned below. It is the responsibility of the manufacturer of the final product to verify whether or not further standards, recommendations or directives are in force outside these areas.

Products intended for sale on US markets¹

ES 59005/ANSI C95.1 Considerations for evaluation of human exposure to Electromagnetic Fields (EMFs) from Mobile Telecommunication Equipment (MTE) in the frequency range 30MHz - 6GHz

Products intended for sale on European markets

EN 50360

Product standard to demonstrate the compliance of mobile phones with the basic restrictions related to human exposure to electromagnetic fields (300MHz - 3GHz)

Please note that SAR requirements are specific only for portable devices and not for mobile devices as defined below:

- · Portable device:
 - A portable device is defined as a transmitting device designed to be used so that the radiating structure(s) of the device is/are within 20 centimeters of the body of the user.
- Mobile device:

A mobile device is defined as a transmitting device designed to be used in other than fixed locations and to generally be used in such a way that a separation distance of at least 20 centimeters is normally maintained between the transmitter's radiating structure(s) and the body of the user or nearby persons. In this context, the term "fixed location" means that the device is physically secured at one location and is not able to be easily moved to another location.

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^{1.} Applies for the quad band module variant EHS5-US only.

5.3 Reference Equipment for Type Approval

The Cinterion Wireless Modules reference setup submitted to type approve EHS5-E/EHS5-US (including a special approval adapter for the DSB75) is shown in the following figure¹:

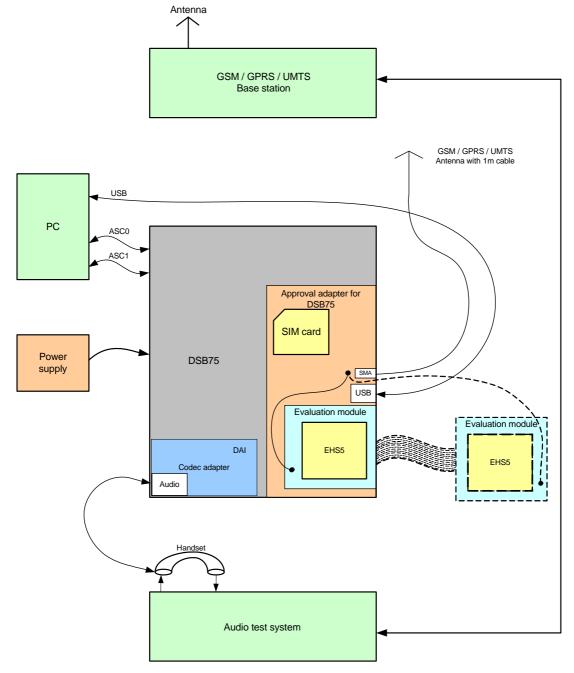


Figure 59: Reference equipment for Type Approval

Hirose SMA-Jack/U.FL-Plug conversion adapter HRMJ-U.FLP(40)

(for details see see http://www.hirose-connectors.com/ or http://www.farnell.com/

Aeroflex Weinschel Fixed Coaxial Attenuator Model 3T/4T

(for details see http://www.aeroflex.com/ams/weinschel/pdfiles/wmod3&4T.pdf)

^{1.} For RF performance tests a mini-SMT/U.FL to SMA adapter with attached 6dB coaxial attenuator is chosen to connect the evaluation module directly to the GSM/UMTS/GPS test equipment instead of employing the SMA antenna connectors on the EHS5-E/EHS5-US-DSB75 adapter as shown in Figure 59. The following products are recommended:

5.4 Compliance with FCC and IC Rules and Regulations

The Equipment Authorization Certification for the Cinterion Wireless Modules reference application described in Section 5.3 will be registered under the following identifiers¹:

FCC Identifier: QIPEHS5-US

Industry Canada Certification Number: 7830A-EHS5US

Granted to Cinterion Wireless Modules GmbH

Manufacturers of mobile or fixed devices incorporating EHS5-US modules are authorized to use the FCC Grants and Industry Canada Certificates of the EHS5-US modules for their own final products according to the conditions referenced in these documents. In this case, an FCC/IC label of the module shall be visible from the outside, or the host device shall bear a second label stating "Contains FCC ID QIPEHS5-US", and accordingly "Contains IC 7830A-EHS5US". The integration is limited to fixed or mobile categorised host devices, where a separation distance between the antenna and any person of min. 20cm can be assured during normal operating conditions. For mobile and fixed operation configurations the antenna gain, including cable loss, must not exceed the limits 3.10 dBi (850 MHz) and 2.50 dBi (1900 MHz).

IMPORTANT:

Manufacturers of portable applications incorporating EHS5-US modules are required to have their final product certified and apply for their own FCC Grant and Industry Canada Certificate related to the specific portable mobile. This is mandatory to meet the SAR requirements for portable mobiles (see Section 5.2 for detail).

Changes or modifications not expressly approved by the party responsible for compliance could void the user's authority to operate the equipment.

Note: This equipment has been tested and found to comply with the limits for a Class B digital device, pursuant to part 15 of the FCC Rules and with Industry Canada licence-exempt RSS standard(s). These limits are designed to provide reasonable protection against harmful interference in a residential installation. This equipment generates, uses and can radiate radio frequency energy and, if not installed and used in accordance with the instructions, may cause harmful interference to radio communications. However, there is no guarantee that interference will not occur in a particular installation. If this equipment does cause harmful interference to radio or television reception, which can be determined by turning the equipment off and on, the user is encouraged to try to correct the interference by one or more of the following measures:

- Reorient or relocate the receiving antenna.
- Increase the separation between the equipment and receiver.
- Connect the equipment into an outlet on a circuit different from that to which the receiver is connected.
- Consult the dealer or an experienced radio/TV technician for help.

This Class B digital apparatus complies with Canadian ICES-003.

If Canadian approval is requested for devices incorporating EHS5-US modules the above note will have to be provided in the English and French language in the final user documentation. Manufacturers/OEM Integrators must ensure that the final user documentation does not contain any information on how to install or remove the module from the final product.

^{1.} Applies only for the quad band module variant EHS5-US.

6 Document Information

6.1 Revision History

Preceding document: "EHS5-E/EHS5-US Hardware Interface Description" Version 01.007b New document: "EHS5-E/EHS5-US Hardware Interface Description" Version **01.007c**

Chapter	What is new
3.2.1	Revised sections describing hardware driven module switch on.
3.2.4.2	New section Disconnect EHS5-E/EHS5-US BATT+ Lines.
4.2	Added note regarding routing of signal tracks.

Preceding document: "EHS5-E/EHS5-US Hardware Interface Description" Version 01.007a New document: "EHS5-E/EHS5-US Hardware Interface Description" Version 01.007b

Chapter	What is new
3.2.1.1	Revised recommended options for possible switch-on circuits as well as ON timings.
4.1	Revised Figure 44 to include tolerances and change module height (2.3mm> 2.2mm).

Preceding document: "EHS5-E/EHS5-US Hardware Interface Description" Version 01.007 New document: "EHS5-E/EHS5-US Hardware Interface Description" Version 01.007a

Chapter	What is new
3.2.1.1	Added serial 100 Ohm resistor to switch for Option 1 shown in Figure 29.

Preceding document: "EHS5-E/EHS5-US Hardware Interface Description" Version 01.000 New document: "EHS5-E/EHS5-US Hardware Interface Description" Version 01.007

Chapter	What is new
Throughout document	GPIO4 shared with fast shutdown line (renamed to FST_SHDN) (available as of Release 2)
2.1.2	AUTO_ON: Added comment to leave line open if not used.
2.1.4, 2.1.5	Extended remark on hardware flow control. Added note for DTR0 line.
2.1.6	Revised description for CCIN signal states in Table 4.
2.1.12.2	Revised resistor values for power indication circuit; see also Figure 28.
3.2.1.1	Revised Figure 29 showing AUTO_ON circuit sample; see also Figure 28.
3.6.1	Added PI pad attenuator circuit to Figure 41.
4	Added remark on Gerber and Step data being available as part of the EHS5-E/EHS5-US documentation package.
4.3.3	Added Figure 58 showing tray dimensions.

Preceding document: "EHS5-E/EHS5-US Hardware Interface Description" Version 00.256a New document: "EHS5-E/EHS5-US Hardware Interface Description" Version 01.000

Chapter	What is new
Throughout document	Renamed ON2 signal to AUTO_ON.
1.1	Added operating temperature values. Revised list of firmware update interfaces. Revised data transfer rates for CSD.
1.3	Added Figure 2 and Figure 3 illustrating module's circuit concept.
2.1.2	Completed signal properties for BATT+, VDDLP, VUSB_IN
2.1.2.1	Extended absolute maximum ratings listed in Table 3.
2.2.1	Completed Table 9 for antenna interface specification.
3.3	Completed section Power Saving.
3.4.1	Completed Table 13 listing power supply ratings.
3.5	Completed Table 14 listing operating temperatures.

Preceding document: "EHS5-E/EHS5-US Hardware Interface Description" Version 00.256 New document: "EHS5-E/EHS5-US Hardware Interface Description" Version 00.256a

Chapter	What is new
2.1.12.2	Revised resistor values in Figure 19.
3.2.1.1	Added new section Switch on EHS5-E/EHS5-US Using AUTO_ON Signal.
3.2.4.1	Revised Figure 35.
5.2, 5.4	Revised sections.

Preceding document: "EHS5-E/EHS5-US Hardware Interface Description" Version 00.000a New document: "EHS5-E/EHS5-US Hardware Interface Description" Version 00.256

Chapter	What is new
2.1.2.1	Revised Table 3.
2.3	Added Figure 28 showing sample application.
3.2.1.1	Revised Figure 30. Added note that ON signal should always be set to low after module startup.
3.4.1	Added power supply ratings to Table 13.
3.6.1	New section ESD Protection for Antenna Interface.

Preceding document: "EHS5-E/EHS5-US Hardware Interface Description" Version 00.000 New document: "EHS5-E/EHS5-US Hardware Interface Description" Version 00.000a

Chapter	What is new
2.1.1	Slightly revised color scheme in Figure 4. Pads 104, 105, 106 are assigned to GND.
2.1.3	Added internal serial resistor (R _S) to Figure 5.
2.1.12.4	New section Fast Shutdown.
3.2.1.1	Revised Figure 29 illustrating an ON circuit sample (value for R2).
7.1	Added ordering information for Multi-Adapter R1 and Approval adapter.

New document: "EHS5-E/EHS5-US Hardware Interface Description" Version 00.000

Chapter	What is new
	Initial document setup.

6.2 Related Documents

- [1] EHS5-E/EHS5-US AT Command Set
- [2] EHS5-E/EHS5-US Release Note
- [3] Application Note 40: Thermal Solutions
- [4] Application Note 48: SMT Module Integration

6.3 Terms and Abbreviations

Abbreviation	Description
ADC	Analog-to-digital converter
AGC	Automatic Gain Control
ANSI	American National Standards Institute
ARFCN	Absolute Radio Frequency Channel Number
ARP	Antenna Reference Point
ASC0/ASC1	Asynchronous Controller. Abbreviations used for first and second serial interface of EHS5-E/EHS5-US
В	Thermistor Constant
BER	Bit Error Rate
BTS	Base Transceiver Station
CB or CBM	Cell Broadcast Message
CE	Conformité Européene (European Conformity)
CHAP	Challenge Handshake Authentication Protocol
CPU	Central Processing Unit

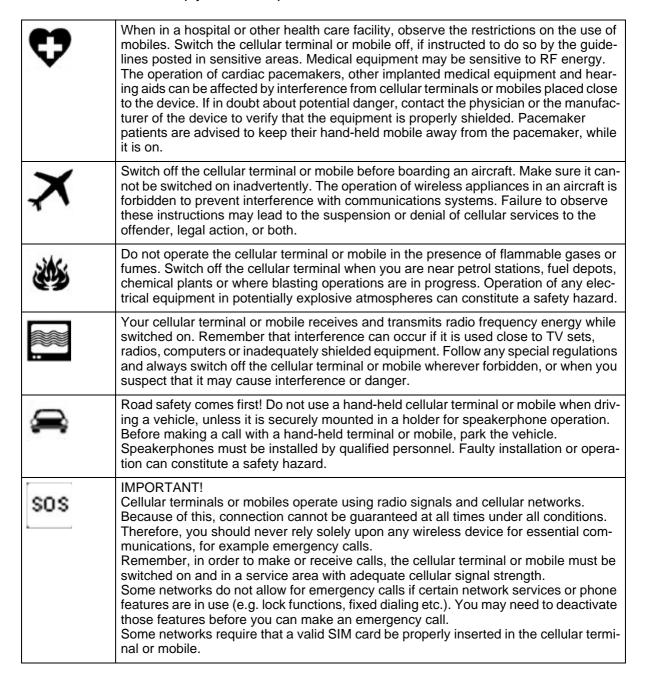
Abbreviation	Description
CS	Coding Scheme
CSD	Circuit Switched Data
CTS	Clear to Send
DAC	Digital-to-Analog Converter
DAI	Digital Audio Interface
dBm0	Digital level, 3.14dBm0 corresponds to full scale, see ITU G.711, A-law
DCE	Data Communication Equipment (typically modems, e.g. Cinterion GSM module)
DCS 1800	Digital Cellular System, also referred to as PCN
DRX	Discontinuous Reception
DSB	Development Support Box
DSP	Digital Signal Processor
DSR	Data Set Ready
DTE	Data Terminal Equipment (typically computer, terminal, printer or, for example, GSM application)
DTR	Data Terminal Ready
DTX	Discontinuous Transmission
EFR	Enhanced Full Rate
EGSM	Enhanced GSM
EIRP	Equivalent Isotropic Radiated Power
EMC	Electromagnetic Compatibility
ERP	Effective Radiated Power
ESD	Electrostatic Discharge
ETS	European Telecommunication Standard
FCC	Federal Communications Commission (U.S.)
FDMA	Frequency Division Multiple Access
FR	Full Rate
GMSK	Gaussian Minimum Shift Keying
GPIO	General Purpose Input/Output
GPRS	General Packet Radio Service
GSM	Global Standard for Mobile Communications
HiZ	High Impedance
HR	Half Rate
I/O	Input/Output
IC	Integrated Circuit
IMEI	International Mobile Equipment Identity
ISO	International Standards Organization
ITU	International Telecommunications Union
kbps	kbits per second
· · · · · · · · · · · · · · · · · · ·	

Abbreviation	Description
LED	Light Emitting Diode
Li-Ion/Li+	Lithium-Ion
Li battery	Rechargeable Lithium Ion or Lithium Polymer battery
Mbps	Mbits per second
MMI	Man Machine Interface
MO	Mobile Originated
MS	Mobile Station (GSM module), also referred to as TE
MSISDN	Mobile Station International ISDN number
MT	Mobile Terminated
NTC	Negative Temperature Coefficient
OEM	Original Equipment Manufacturer
PA	Power Amplifier
PAP	Password Authentication Protocol
PBCCH	Packet Switched Broadcast Control Channel
PCB	Printed Circuit Board
PCL	Power Control Level
PCM	Pulse Code Modulation
PCN	Personal Communications Network, also referred to as DCS 1800
PCS	Personal Communication System, also referred to as GSM 1900
PDU	Protocol Data Unit
PLL	Phase Locked Loop
PPP	Point-to-point protocol
PSK	Phase Shift Keying
PSU	Power Supply Unit
PWM	Pulse Width Modulation
R&TTE	Radio and Telecommunication Terminal Equipment
RAM	Random Access Memory
RF	Radio Frequency
RLS	Radio Link Stability
RMS	Root Mean Square (value)
RoHS	Restriction of the use of certain hazardous substances in electrical and electronic equipment.
ROM	Read-only Memory
RTC	Real Time Clock
RTS	Request to Send
Rx	Receive Direction
SAR	Specific Absorption Rate
SAW	Surface Accoustic Wave

Abbreviation	Description
SELV	Safety Extra Low Voltage
SIM	Subscriber Identification Module
SMD	Surface Mount Device
SMS	Short Message Service
SMT	Surface Mount Technology
SRAM	Static Random Access Memory
TA	Terminal adapter (e.g. GSM module)
TDMA	Time Division Multiple Access
TE	Terminal Equipment, also referred to as DTE
TLS	Transport Layer Security
Тх	Transmit Direction
UART	Universal asynchronous receiver-transmitter
URC	Unsolicited Result Code
USSD	Unstructured Supplementary Service Data
VSWR	Voltage Standing Wave Ratio

6.4 Safety Precaution Notes

The following safety precautions must be observed during all phases of the operation, usage, service or repair of any cellular terminal or mobile incorporating EHS5-E/EHS5-US. Manufacturers of the cellular terminal are advised to convey the following safety information to users and operating personnel and to incorporate these guidelines into all manuals supplied with the product. Failure to comply with these precautions violates safety standards of design, manufacture and intended use of the product. Cinterion Wireless Modules assumes no liability for customer's failure to comply with these precautions.



7 Appendix

7.1 List of Parts and Accessories

Table 26: List of parts and accessories

Description	Supplier	Ordering information	
EHS5-E/EHS5-US	Cinterion	Standard module Cinterion Wireless Modules IMEI: Packaging unit (ordering) number: L30960-N2800-A100 (EHS5-E) L30960-N2810-A100 (EHS5-US) Module label number: S30960-S2800-A100-1 (EHS5-E) S30960-S2810-A100-1 (EHS5-US) Customer IMEI mode: Packaging unit (ordering) number: L30960-N2805-A100 (EHS5-E) L30960-N2815-A100 (EHS5-US) Module label number: S30960-S2805-A100-1 (EHS5-E) S30960-S2815-A100-1 (EHS5-US)	
DSB75 Evaluation Kit	Cinterion	Ordering number: L36880-N8811-A100	
Multi-Adapter R1 for mounting EHS5-E/EHS5-US evaluation modules onto DSB75	Cinterion	Ordering number: L30960-N0010-A100	
Approval adapter for mounting EHS5-E/EHS5-US evaluation modules onto DSB75	Cinterion	Ordering number: L30960-N2301-A100	
Evaluation Module	Cinterion	Ordering number: L30960-N2801-A100 (EHS5-E) Ordering number: L30960-N2811-A100 (EHS5-US)	
Votronic Handset	VOTRONIC / Cinterion	Cinterion ordering number: L36880-N8301-A107 Votronic ordering number: HH-SI-30.3/V1.1/0 VOTRONIC Entwicklungs- und Produktionsgesellschaft für elektronische Geräte mbH Saarbrücker Str. 8 66386 St. Ingbert Germany Phone: +49-(0)6 89 4 / 92 55-0 Fax: +49-(0)6 89 4 / 92 55-88 Email: contact@votronic.com	
SIM card holder incl. push button ejector and slide-in tray	Molex	Ordering numbers: 91228 91236 Sales contacts are listed in Table 27.	

Table 27: Molex sales contacts (subject to change)

Molex For further information please click: http://www.molex.com	Molex Deutschland GmbH Otto-Hahn-Str. 1b 69190 Walldorf Germany Phone: +49-6227-3091-0 Fax: +49-6227-3091-8100 Email: mxgermany@molex.com	American Headquarters Lisle, Illinois 60532 U.S.A. Phone: +1-800-78MOLEX Fax: +1-630-969-1352
Molex China Distributors Beijing, Room 1311, Tower B, COFCO Plaza No. 8, Jian Guo Men Nei Street, 100005 Beijing P.R. China Phone: +86-10-6526-9628 Fax: +86-10-6526-9730	Molex Singapore Pte. Ltd. 110, International Road Jurong Town, Singapore 629174 Phone: +65-6-268-6868 Fax: +65-6-265-6044	Molex Japan Co. Ltd. 1-5-4 Fukami-Higashi, Yamato-City, Kanagawa, 242-8585 Japan Phone: +81-46-265-2325 Fax: +81-46-265-2365

About Gemalto

Gemalto (Euronext NL0000400653 GTO) is the world leader in digital security with 2011 annual revenues of €2 billion and more than 10,000 employees operating out of 74 offices and 14 Research & Development centers, located in 43 countries.

We are at the heart of the rapidly evolving digital society. Billions of people worldwide increasingly want the freedom to communicate, travel, shop, bank, entertain and work - anytime, everywhere - in ways that are enjoyable and safe. Gemalto delivers on their expanding needs for personal mobile services, payment security, authenticated cloud access, identity and privacy protection, eHealthcare and eGovernment efficiency, convenient ticketing and dependable machine-to-machine (M2M) applications.

Gemalto develops secure embedded software and secure products which we design and personalize. Our platforms and services manage these secure products, the confidential data they contain and the trusted end-user services they enable. Our inovations enable our clients to offer trusted and convenient digital services to billions of individuals.

Gemalto thrives with the growing number of people using its solutions to interact with the digital and wireless world.

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